

10/19/00
jc685 U.S. PTO

NONPROVISIONAL PATENT
APPLICATION TRANSMITTAL RULE §1.53(b)
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

ARENT FOX KINTNER PLOTKIN & KAHN, PLLC
1050 Connecticut Avenue, N.W.,
Suite 600
Washington, DC 20036-5339
Telephone: (202) 857-6000
Facsimile: (202) 638-4810

Docket No. P108066-00014

Date: October 19, 2000

jc682 U.S. PTO
09/691115
10/19/00

Commissioner for Patents
Washington, D.C. 20231

Sir:

Transmitted herewith for filing under 37 C.F.R. §1.53(b) is a nonprovisional patent application:

For (Title): SELF-TEST CIRCUIT AND MEMORY DEVICE INCORPORATING IT

By (Inventors): Yukihiro NOMURA; Hiroyuki FUJIMOTO; Takahiro SUZUKI; Tatsuya KANDA; Yasurou MATSUZAKI; Masahiko SAITOU; Hiroyoshi TOMITA

- ☒ 67 pages of Specification/Claims 1-39/Abstract are attached.
- ☒ Formal drawings (Fig. 1-30; 30 sheet(s) is attached.
- ☒ A Declaration and Power of Attorney is attached.
- ☒ An assignment of the invention to Fujitsu Limited is attached, along with Form PTO-1595 and a check for \$40.00.
- ☒ An Information Disclosure Statement is attached, along with Form PTO-1449, and 2 reference(s).
- ☐ A Statement to establish small entity status under 37 C.F.R. §§1.9 and 1.27 is attached.
- ☒ A Preliminary Amendment is attached.
- ☐ Please amend the specification by inserting before the first line the sentence This nonprovisional application claims the benefit of U.S. Provisional Application No., filed.
- ☒ Priority of foreign application No(s). 11-359999 & 2000-169689 filed December 17, 1999 & June 6, 2000 in Japan is claimed under 35 U.S.C. §119.
- ☒ A certified copy of the above corresponding foreign applications is attached.

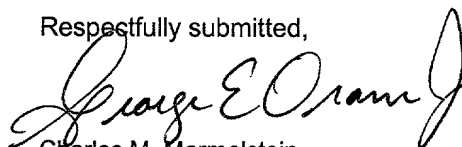
The filing fee is calculated below and includes claim status after entry of any Preliminary Amendment noted above:

FOR:	NO. FILED	NO. EXTRA
BASIC FEE		
TOTAL CLAIMS	43 - 20	= 23
INDEP CLAIMS	3 - 3	= 0
<input checked="" type="checkbox"/> MULTIPLE DEPENDENT CLAIMS		

SMALL ENTITY			LARGE ENTITY	
RATE	FEE	OR	RATE	FEE
	\$ 355	OR		\$ 710
x 9 =	\$	OR	x 18	\$ 414
x 40 =	\$	OR	x 80	\$ 0
+135 =	\$	OR	+270	\$ 270
TOTAL	\$	OR	TOTAL	\$ 1394

- ☐ A check for the filing fee is not enclosed at this time.
- ☒ A check in the amount of \$1434.00 is attached. Please charge any fee deficiency or credit any overpayment to Deposit Account No. 01-2300.

Respectfully submitted,



Charles M. Marmelstein
Registration No. 25,895

27931

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

NOMURA et al.

Application No.: New Appln.

Filed: October 19, 2000

Attorney Dkt. No.: P108066-00014

For: SELF-TEST CIRCUIT AND MEMORY DEVICE INCORPORATING IT

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Date: October 19, 2000

Sir:

Prior to initial examination of the application, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

Page 10, line 23, delete "Figure 15 is an operation timing chart of a test" and substitute therefore, -- Figure 15A-15C is an operation timing chart of a test --

Page 11, line 11, delete "Figure 21 is a view showing an example of an output" and substitute therefore, -- Figure 21A and 21B is a view showing an example of an output --

Page 12, line 3, delete "Figure 29 is a view illustrating the reset function" and substitute therefore, -- Figure 29A-29C is a view illustrating the reset function --

REMARKS

Claims 1-39 are pending in this application. No new matter is contained in the amendments.

Please charge any fee deficiency or credit any overpayment to Deposit Account No. 01-2300.

Respectfully submitted,



Charles M. Marmelstein
Registration No. 25,895

27931

ARENT FOX KINTNER PLOTKIN & KAHN, PLLC
1050 Connecticut Avenue, N.W.,
Suite 600
Washington, D.C. 20036-5339
Tel: (202) 857-6000
Fax: (202) 638-4810

SELF-TEST CIRCUIT AND MEMORY DEVICE INCORPORATING IT

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to a self-test circuit for self-diagnosis incorporated in a memory device and in particular relates to a self-test circuit whereby self-test can be performed utilizing comparatively few input/output terminals. The present invention relates for example to self-test circuits that are suitable for burn-in testing in the wafer processing step.

2. Description of the Related Art

In recent years, memory devices such as dynamic RAM (DRAM) have been increased in capacity and scale. Concomitantly, the cost of the testing step in which inspection for failed bits within the memory is performed using an LSI tester has increased, resulting in increased costs of the memory device.

Figure 1 is a typical layout diagram of a prior art memory device. Figure 1 shows a typical layout taking the example of a synchronous DRAM (SDRAM). In the example of Figure 1, a clock CLK is supplied to clock input buffer 10 from outside, and an internal clock I-CLK is supplied to each circuit block. Also, command input CMD is supplied to command decoder 12 from outside, the decoded external

command CMD is latched in command latch circuit 16, and
a control circuit 18 controls the circuitry within memory
bank MBNK, which is the memory core, in response to this
latched external command. Also, addresses A0 to An are
5 supplied to address buffer 14 from outside, and its address
EXADD is supplied to memory buffer MBNK.

A memory bank MBNK is divided into, for example, a
plurality of memory blocks BLK; in each memory block there
are provided a row decoder RDEC, a memory cell array MCA,
10 a sensing amplifier SA, and a column decoder CDEC etc.
Furthermore, the memory blocks are connected to a sensing
buffer and write amplifier SB/WA through a database DB and
are furthermore connected to an input/output terminal DQ
through a data input/output circuit DI/O.

15 Furthermore, although not shown in the drawing, within
memory bank MBNK, there are provided redundant cells that
are capable of replacing failed bits. Failed bits detected
by an operation test are replaced by these redundant cells,
and shipped as a passed chip.

20 In a conventional testing step in which failed bits
are detected prior to shipping, an LSI tester supplies from
command input terminal CMD, address terminals A0 to An and
input/output terminal DQ the operating commands, addresses,
and write data etc that are required for testing, and checks
25 whether or not the read data that is output from input/output
terminal DQ is the expected data. Consequently, for example
when performing a test of whether data 1 can be read or

not by writing data 1, the LSI tester performs writing using an active command, write command, reset command, non-select command etc, and performs reading using an active command, read command, reset command, and de-select command etc.

5 This test step using an LSI tester is usually performed after the LSI chip has been accommodated in the package in the assembly step, which is a later step.

However, in the above defect testing step, it is necessary to employ an LSI tester, and a long time is required due to the increased capacity of memory. It has therefore been proposed to incorporate within a memory device a testing circuit for self-diagnosis, in order to perform the above defect test without using an LSI tester. Such a self-test circuit is called a "Built-In Self-Test (BIST) circuit (hereinbelow referred to simply as BIST circuit).

However, no consensus has yet been reached as to what construction of such a BIST circuit is most suitable. For example, if a BIST circuit is incorporated in a memory device but simply outputs "pass" or "fail" of the test, it is impossible to ascertain the number of failed bits, and so it is not possible to decide whether or not a rescue function utilizing redundant cells can be utilized. If, on the other hand, the BIST circuit stores all the addresses of failed bits, the BIST circuit itself becomes of large scale and so impracticable.

In contrast, the prior art method in which failed products that were incapable of being rescued by redundant

cells were excluded by performing a diagnostic test after the subsequent step (assembly step) of the manufacturing step did not make a sufficient contribution to lowering device costs. Rescuing failed products by utilizing
5 redundant cells converts failed products into passed products, and so contributes to lowering of costs to a certain extent. However, if the defect test is performed after the assembly step, the proportion of costs relating to the assembly step of devices that finally end up as failed
10 products is wasted.

In order to solve such problems, it has been proposed to perform the burn-in test (accelerated test) in the preceding step (wafer level) of the manufacturing step. However, the testers for the accelerated test at the wafer
15 stage have only a small number of probes that can be utilized, so it is difficult to perform a complicated function test such as was performed with the conventional LSI tester. It is therefore desirable to incorporate in the memory device a self-test circuit that can be utilized in the
20 burn-in test at wafer level.

SUMMARY OF THE INVENTION

Accordingly, an object of the present invention is to provide a self-test circuit incorporated in a memory device
25 that is adapted for rescue of failed products by utilizing redundant cells.

Also, a further object of the present invention is to

provide a self-test circuit incorporated in a memory device that is capable of being operated by means of a small number of external terminals.

Yet a further object of the present invention is to provide a self-test circuit incorporated in a memory device that is capable of being utilized in a burn-in test at the wafer stage.

Yet a further object of the present invention is to provide a memory device incorporating a self-test circuit as described above.

In order to achieve the above objects, one aspect of the present invention is a self-test circuit incorporated in the memory device, which is activated in response to a test activation signal from outside. When this self-test circuit is activated in response to a test activation signal from outside, it generates a test operation command, generates a test address, and generates test data. Furthermore, after the self-test circuit writes the test data to a memory cell, it effects a comparison to establish whether or not the read data that is read from this memory cell is the same as the test data that was written thereto and stores information as to the result of this comparison. This comparison result information is then output to the outside.

A memory device that incorporates the self-test circuit is preferably provided with a self-test external terminal. A test activation signal is supplied from this self-test

external terminal, a command for test purposes is supplied thereto, and the comparison result information can be output therefrom.

For the defect test, it is possible to employ for example
5 (1) a scan pattern wherein prescribed test data are written to all the memory cells whilst incrementing the address, then all the memory cells are read, and a check is made to establish that the read data are the same as the test data, or (2) a march pattern, in which prescribed test data
10 are written to all the memory cells whilst incrementing the address and then inverted test data are written whilst reading all the memory cells, then inverted test data are again written whilst reading all the memory cells while the address is decremented, and finally all the memory cells
15 are read while the address is incremented.

Basically, these defect detection test patterns involve repeated reading and writing operations. In order to generate these test patterns automatically, the self-test circuit comprises a function of generating a
20 write or read test operation command, a function of generating a test address, a function of generating test data and a function of comparing whether or not the read data coincide with the test data. In this way, this incorporated self-test circuit can automatically perform
25 self-test internally by being supplied from outside with restricted signals utilizing restricted input/output terminals.

Preferably this self-test circuit is capable of outputting, as comparison result information, information as to whether or not rescue can be achieved by means of redundancy, so that the yield can be improved by utilizing
5 redundant cells within the memory device. For example, the circuit that accumulates the comparison result is preferably provided with a function of counting the number of failed bits. Alternatively, the circuit that accumulates the comparison result is preferably provided with a
10 function of outputting information as to whether or not the number of failed bits exceeds the number that can be rescued by redundant cells.

Furthermore, this self-test circuit is preferably provided with an operation mode selector circuit such as
15 to be capable of designating the test operation mode from outside to some degree. The march pattern and/or scan pattern tests mentioned above can be implemented by combining these test operation modes. In this case, the operation of the memory core is controlled by generating
20 an active command, read command, pre-charge command, disable command (non-selected command) etc internally in accordance with the test operation mode.

Alternatively, as a further example, the self-test circuit is preferably provided with an operation mode
25 selector circuit capable of sequentially shifting automatically to various test operation modes in response to activation. In this case, it is unnecessary to provide

a signal from outside to specify the test operation mode. In the case of this example, the test operation mode that is necessary for the test pattern is sequentially selected simply by applying from outside a test pattern such as a scan pattern or march pattern.

In a preferred embodiment, in a self-test mode, this self-test circuit executes self-test by generating a test address, test data and test operation command. Consequently, there is provided a selector that changes over between an address, write data and operation command from outside and a test address, test data and test operation command generated internally. Preferably at least a or some selectors are provided within an input circuit that inputs an external address, write data, or operation command. The reason for adopting such a construction is that more internal circuits can be made the subject of testing when performing a burn-in test.

If a selector circuit is provided in an input circuit as described above, the input circuit inputs an input signal that is changed over by the selector in synchronization with a first clock, while the self-test circuit supplies to the selector a test command, test address, and test data signal in synchronization with a second clock whose phase is advanced from said first clock. In this way, the input circuit can reliably input the test command, test address and test data signal that are internally generated.

Furthermore, if a selector circuit is provided within

an input circuit as described above, when changeover to self-test mode is effected by an ordinary external command, the selector is changed over to the self-test signal side, and input of a self-test cancellation command becomes impossible. Accordingly, in a preferred embodiment, in self-test mode, there is provided a construction whereby at least a or some selectors are changed over to the external input terminal side in response to a certain condition of a prescribed external terminal.

Furthermore, in a further embodiment, there is provided a construction whereby a reset signal is supplied to the internal circuitry including at least the memory core and/or memory control circuit in response to a reset command supplied from the self-test input terminal, resetting of the internal circuitry being thereby effected. When a burn-in test is performed at wafer level, it is necessary to reset the internal circuitry by means of a reset command from a self-test input terminal provided as the terminal for self-test purposes. In this case, this self-test circuit itself is not reset.

BRIEF DESCRIPTION OF THE DRAWINGS

Figure 1 is a layout diagram of a prior art memory device;

Figure 2 is a layout diagram of a memory device according to an embodiment;

Figure 3 is a circuit diagram illustrating a WBI activation circuit, WBI input buffer, and WBI mode selector

circuit;

Figure 4 is an operation timing chart of entry into the self-test step;

Figure 5 is an operation timing chart on output of test
5 result information;

Figure 6 is a view showing the operation of march constituting an example of a test pattern;

Figure 7 is an operation timing chart of a test operation mode MODE1;

10 Figure 8 is an operation timing chart of a test operation mode MODE2;

Figure 9 is an operation timing chart of a test operation mode MODE3;

15 Figure 10 is an operation timing chart of a test operation mode MODE4;

Figure 11 is an operation timing chart of a test operation mode OUTPUT;

Figure 12 is a circuit diagram of a WBI control circuit;

20 Figure 13 is a circuit diagram of a WBI command generating circuit;

Figure 14 is a circuit diagram of a test address/data generating circuit;

Figure 15 is an operation timing chart of a test address/data generating circuit;

25 Figure 16 is a layout diagram of a data comparison unit, counter, parallel/serial conversion unit, and test output buffer;

Figure 17 is an operation timing chart of a data comparison unit;

Figure 18 is a layout diagram of a memory device according to a second embodiment;

5 Figure 19 is a layout diagram of a memory device incorporating a self-test circuit according to a third embodiment;

10 Figure 20 is a layout diagram of a WBI activation circuit and WBI mode selection circuit according to a fourth embodiment;

Figure 21 is a view showing an example of an output unit for test result information according to a fifth embodiment;

15 Figure 22 is a layout diagram of a memory device according to a sixth embodiment;

Figure 23 is a view illustrating the layout of an input circuit according to a seventh embodiment;

20 Figure 24 is a timing chart illustrating the relationship between generation and input of test addresses;

Figure 25 is a timing chart illustrating entry and cancellation of self-test mode after assembly;

Figure 26 is a circuit diagram of a WBI activation circuit according to the seventh embodiment;

25 Figure 27 is a layout diagram of a further input circuit according to the seventh embodiment;

Figure 28 is a timing chart illustrating entry and

cancellation of self-test mode after assembly in the case of Figure 27;

Figure 29 is a view illustrating the reset function according to an eighth embodiment; and

5 Figure 30 is a view illustrating a WBI mode selector circuit according to the eighth embodiment.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

Embodiments of the present invention are described below with reference to the drawings. However, the technical scope of the present invention is not restricted to such embodiments.

10 Figure 2 is a layout diagram of a memory device according to an embodiment. The memory device illustrated in Figure 2, in addition to memory circuit layout identical with that of the prior art example of Figure 1, incorporates a self-test circuit BIST (Built In Self-test). It is a precondition of the self-test circuit BIST in this embodiment that it can be used in the wafer level burn-in (herein below abbreviated to WBI) step. Since there are limitations on the number of probes that can be utilized per chip in the wafer level burn-in test, a self-test circuit BIST that is capable of performing self-diagnosis in which the number of failed bits is detected notwithstanding such
15
20
25 restrictions on the number of probes will be described. However, this self-test circuit BIST can be utilized not just in the wafer level burn-in test but also in test steps

subsequent to the assembly step.

Also, there are for example four types of test operation mode in self-test. Firstly, there is the mode (MODE1) in which data is written while incrementing the address;
5 secondly, there is the mode (MODE2) in which, simultaneously with reading data from memory while incrementing the address, data which are the inverse thereof are written; thirdly, there is the mode in which, simultaneously with reading data from memory while
10 decrementing the address, data which are the inverse thereof are written (MODE3); and fourthly there is the mode in which data are read from memory while incrementing the address (MODE4). Apart from these, self-test also requires a mode in which the test results are output externally.
15 Various test patterns can be implemented by combining the above four test operation modes. The details of these will be described later.

In order to implement the various test operation modes, it is necessary to generate operation commands for reading
20 or writing of the memory device and to apply these to the memory device. Describing for example the case of an SDRAM (synchronous DRAM), in the first mode MODE1, it is necessary to apply to the memory device continuously at each address the active command, write command, pre-charge command, and
25 deselect command. Also, in the case of an FCRAM (Fast Cycle RAM), it is necessary to apply operation commands such as active write and active read. The operation commands that

are utilized in ordinary operation by the memory device are generated by the self-test circuit and supplied to the control circuitry of the memory.

The memory circuit portion of Figure 2 is the same as that of the prior art example of Figure 1 and the same reference numerals are applied thereto. In memory bank MBNK, which is the core memory, a redundant memory cell array, not shown, which can replace failed bits, is provided adjacent to the ordinary memory cell array.

In the self-test circuit BIST of the embodiment shown in Figure 2, there are provided: (1) a WBI activation circuit 20 for activating self-test circuit BIST in response to an activation signal WBIZ from outside, (2) a test operation mode selector circuit 22 for selecting a test operation mode in accordance with an operation mode input signal BISTZ from outside, (3) a WBI control circuit 24 for generating a test clock etc constituting a control signal and/or timing signal in accordance with the test operation mode signal \emptyset MODE, (4) a WBI command generating circuit 26 for generating a test operation command WBI-CMD corresponding to the test operation mode, (5) a WBI address/data generating circuit 28 for generating test addresses WBI-ADD and test data WBI-DATA corresponding to the test operation mode, (6) a data comparison unit 30 for comparing the read output data DOUT from a memory cell with the test data WBI-DATA and generating a fail signal \emptyset F if these are different, (7) a failed bit counter 32 for counting as test

result information the number of times the fail signal ϕF is generated, (8) a parallel-serial conversion circuit 34, and (9) a WBI output buffer 36 that outputs the serial data.

The above test operation command WBI-CMD is supplied to control circuit 18 in the memory device through selector 40. Likewise, the test address WBI-ADD is supplied to the memory core (memory bank) MBNK in the memory device through selector 41, and test data WBI-DATA is supplied to write amplifier WA through selector 42. These selectors 40, 41, 42 are changed over to respective signals from self-test circuit BIST by a start signal $\phi START$ that is generated by test control circuit 24 when in each test operation mode. During ordinary operation, the external command CMD from command latch 16, the external address EXADD from address buffer 14, and input data DIN from data input/output circuit DI/O are respectively selected and supplied to the memory core etc.

Consequently, in normal operation, the signal a side is selected at each selector, and normal operation is performed in accordance with the external operation command CMD, external address EXADD, and input data DIN.

Then, in for example a wafer level burn-in test, WBI activation circuit 20 generates an activation signal ϕWBI by supplying activation signal WBIZ, thereby activating test operation mode selector circuit 22 and WBI control circuit 24. Test operation mode selector circuit 22 selects the test operation mode by decoding the mode input signal

BISTZ that is serially input from outside and applied thereto through WBI input buffer 21. That is, test operation mode selector circuit 22 generates test operation mode signal \emptyset MODE. In response to this test operation mode signal \emptyset MODE, WBI control circuit 24 respectively supplies first test clock WBI-CLK1 and second test clock WBI-CLK2 for test operation purposes to WBI command generating circuit 26 and WBI address/data generating circuit 28, and generates the start signal \emptyset START of each test operation mode.

In response to this start signal \emptyset START, selectors 40, 41, 42 select the signal b side. Then, WBI command generating circuit 26 generates test operation command WBI-CMD in accordance with the test operation mode, with the timing of the first test clock WBI-CLK1. Also, WBI address/data generating circuit 28 generates test address WBI-ADD and test data WBI-DATA in accordance with the test operation mode, with the timing of the second test clock WBI-CLK2. The memory circuit executes read operation and/or write operation in accordance with the test operation mode, in response to the supply of these test operation commands, test addresses and test data. Data comparison unit 30 compares the output data DOUT that is read from the memory cell with the test data WBI-DATA that is written and the fail signal \emptyset F that is generated in the event that these do not coincide is counted by counter 32. This count value is subjected to parallel/serial conversion, and is output serially from signal terminal BISTZ by test output buffer

36.

The output terminal that is supplied with the above activation signal WBIZ and the signal terminal BISTZ are special external terminals that are utilized only during for example a wafer level burn-in test. These terminals WBI, BISTZ, clock terminal CLK and power source terminal are terminals necessary during WBI testing and are constituted such that the self-test circuit BIST can cope with the restrictions on the number of probes.

Next, entry of the self-test step and output of the test result information will be described. Figure 3 is a circuit diagram showing the WBI activation circuit, WBI input buffer, and WBI mode selector circuit. Also, Figure 4 is a timing chart of operation on entry into the self-test step, and Figure 5 is a timing chart of operation during output of the test result information.

WBI activation circuit 20 comprises a resistance 45 whereby terminal WBIZ that is supplied with the activation signal is connected to ground Vss and inverters 46, 47. Consequently, when terminal WBIZ is in open condition, the WBI activation signal ϕ WBI is made L level by resistance 45 and the NAND gates 48, 49 in WBI input buffer 21 are closed. When an H level activation signal WBIZ is applied, the internal WBI activation signal ϕ WBI becomes H level, putting the NAND gates 48, 49 in WBI input buffer 21 in open condition, so that the clock I-CLK and mode input signal BISTZ are respectively passed. Consequently, during

self-test, the activation signal WBIZ from outside is maintained at H level.

In synchronization with the clock I-CLK, WBI mode selector circuit 22 serially inputs the mode input signal BISTZ, decodes it, and generates the corresponding WBI mode signal ϕ MODE. For this purpose, WBI mode selector circuit 22 is provided with a shift register 52 that is supplied with mode input signal BISTZ that is transferred serially thereto by way of WBI input buffer 21, transfer gate 54 that transfers the mode input signals BISTZ of a plurality of bits, latch circuit 56, and decoder 58.

As shown in Figure 4, mode input signal BISTZ is constituted by a single-bit entry code 69 and 5-bit mode code 70. In order to enter each test mode of the self-test step, entry code 69 is set to "1" and subsequently the mode code 70 is supplied in serial fashion. The mode code 70 is set in correspondence with a plurality of test operation modes as shown in the Table of Figure 4. For example, in the case of the second test operation mode MODE2, as the mode input signal BISTZ, "110001" is input to shift register 52. Consequently, when all 6 bits are supplied to shift register 52, transfer pulse generating unit 62 generates a transfer signal S62, causing transfer gate 54 to transfer the mode code 70 of the mode input signal BISTZ in shift register 52 to latch circuit 56. Then, in response to transfer signal S62, reset pulse generating unit 60 generates a reset signal S60, causing shift register 52

to be reset. The mode code that is latched in latch circuit 56 is then decoded by decoder 58 and, as shown in the Table of Figure 4, one or other of the corresponding test operation mode signals ϕ MODE is thereby made H level.

5 When the various test operation modes are executed, one or other of the end signals END1, END2 becomes an H level pulse, the condition of latch circuit 56 is latched by reset signal S65, and all of the test operation mode signals ϕ MODE become L level.

10 Figure 5 is an operation timing chart on output of the test result information. In period t0, when "110010" is supplied as mode input signal BISTZ, as shown in the corresponding Table of Figure 4, the output mode OUTPUT corresponding to mode code "10010" becomes H level. The test operation mode signal OUTPUT is also supplied to three clock pulse delay circuit 66 and NOR gate 67, and mode input control signal S68 becomes H level. The H level of this signal S68 puts NOR gate 50 in closed condition, thereby inhibiting input of the mode input signal BISTZ. That is, 15 in period t3, input of mode input signal BISTZ is disabled. In period t3, the input-disabled condition continues also for a period t2 of three clock pulses after the output mode signal OUTPUT has become L level.

20 In addition, in the self-test step, the input terminal BISTZ is employed as an output terminal. Consequently, in the period t3, both input and output are disabled during the initial period of three clock pulses t1 and final period 25

of three clock pulses t_2 , thereby avoiding conflict of input and output at terminal BISTZ. That is, in periods t_1 and t_2 , terminal BISTZ goes into H impedance condition in order to effect changeover of input and output.

5 As shown in Figure 5, WBI output buffer circuit 36 outputs from terminal BISTZ H level signal "1" for output recognition and following this the count value of failed bit counter 32 in serial fashion. When the end signal END2 is supplied from parallel/serial conversion circuit 34,
10 the latch condition is reset in WBI mode selection circuit 22 by supplying the reset signal S65 through NOR gate 64 and inverter 65 to latch circuit 56. Accompanying this, the output mode signal OUTPUT becomes L level, and the mode input control signal S68 becomes L level after a period
15 t_2 of three clock pulses, with the result that input of mode input signal BISTZ is enabled.

Next, the test patterns, test operation modes, and the test operation commands associated therewith will be described. Figure 6 is a view showing the operation of march,
20 which is one example of a test pattern. march is a test pattern in which the four test operation modes MODE1, 2, 3, 4 described above and the output mode OUTPUT are sequentially executed.

Specifically, in march, as shown in Figure 6, first
25 of all, the first mode MODE1 is executed, in which data is written while incrementing the address; next, the second mode MODE2 is executed in which data which are the inverse

of this are written at the same time as data are read from the memory cells, whilst incrementing the address; next, the third mode MODE3 is executed, in which data which are the inverse thereof are written simultaneously with reading the data from the memory cells while decrementing the address; next, the fourth mode MODE4 is executed, in which data are read from the memory cells whilst incrementing the address. Finally, in the output mode OUTPUT, the failed bit information accumulated in failed bit counter 32 is output.

Figure 6 shows an example of the test data WBI-DATA in each test operation mode. If (1) is assumed to be the uninverted pattern, (2) is the inverted pattern, which is the inverse thereof. In the case of the uninverted pattern (1), for example a checkered pattern of "0" and "1" as shown in the drawing is written (W in the drawing) to adjacent memory cells, and is read (R in the drawing). The test data WBI-DATA that was written in the first mode MODE1 is read in the second mode MODE2, and the inverted data thereof is written. In addition, in the third mode MODE3, the inverted data that was written in the second mode MODE2 is read, and the inverted data thereof is written. Then, in the final fourth mode MODE4, the inverted data thereof is read. As shown in Figure 6, the test addresses WBI-ADD in each mode are sequentially incremented, incremented, decremented, and incremented.

In the march pattern, either the four modes MODE1 to

4 may be executed only in the aforementioned uninverted pattern or the respective four modes MODE1 to 4 may be executed in the aforementioned uninverted pattern and inverted pattern. Consequently, if the test is executed using just the uninverted pattern, if a single bit in the memory core is defective, the defect is detected once on each occasion during the three READ operations in the four test operation modes, with the result that a total of three fail signals $\emptyset F$ are generated. If the respective four test operation modes are executed in both the uninverted pattern and inverted pattern, a total of six fail signals $\emptyset F$ are generated.

Figure 7 to Figure 10 are operation timing charts of the four test operation modes. In the first mode MODE1 shown in Figure 7, data WBI-DATA is written to the memory cells while incrementing the test addresses WBI-ADD. To achieve this, the test operation commands active ACTV, write WR, pre-charge PRE, and deselect DSEL are successively generated in synchronization with the first test clock WBI-CLK1, which is synchronized with the clock I-CLK. Concurrently, the test address WBI-ADD is sequentially incremented from A0 in synchronization with the second test clock WBI-CLK2, which is obtained from the clock I-CLK by frequency division of 1/4. Also, for the test data WBI-DATA, the prescribed data shown in Figure 6 are generated. In the first mode MODE1, the read operation is not performed, so the read enable signal \emptyset RENB stays at L level and the

third test clock WBI-CLK3 that is supplied to the serial/parallel conversion circuit 34 and WBI output buffer 36 also stays at L level.

In the second mode MODE2 shown in Figure 8, data WBI-DATA is read from the memory cells whilst incrementing the test address WBI-ADD, and inverted data WBI-DATA is written to the memory cells. To achieve this, reading is performed by successively generating the test operation commands active ACTV, read RD, pre-charge PRE, and deselect DSEL in synchronization with the first test clock WBI-CLK1, which is synchronized with the clock I-CLK. In addition, writing is performed by successively generating active ACTV, write WR, pre-charge PRE and deselect DSEL.

The aforementioned reading and writing are alternately repeated in synchronization with the second test clock WBI-CLK2, which is obtained by frequency division of clock I-CLK to 1/8. Accompanying this, the read enable signal ϕ RENB also alternately repeats H level (read enabled) and L level (read disabled) in synchronization with second test clock WBI-CLK 2. Also, test address WBI-ADD is sequentially incremented from A0 in synchronization with the second test clock WBI-CLK2. Also, the test data WBI-DATA, in the read-enabled condition (ϕ RENB=H), is set to the first data "0" as expected value and, in the write condition (ϕ RENB=L), is set to the second data "1", which is the inverse thereof, as write data. It should be noted that the first data and second data may be for example mutually inverted checkered

patterns as illustrated in Figure 6.

In the third mode MODE3 shown in Figure 9, data WBI-DATA is read from the memory cells whilst decrementing the test address WBI-ADD, and the inverted data WBI-DATA is written to these memory cells. Consequently, the difference from the second mode MODE2 is that the test address WBI-ADD is decremented from An in synchronization with the second test clock WBI-CLK2 and that the test data WBI-DATA, in the read-enabled condition ($\emptyset\text{RENB}=\text{H}$), is set to the second data "1" as expected value and, in the write condition ($\emptyset\text{RENB}=\text{L}$), is set to the first data "0", which is the inverse of this, as write data.

In the fourth mode MODE4 shown in Figure 10, the data WBI-DATA is read from the memory cells whilst incrementing the test address WBI-ADD. Consequently, reading is performed by successively generating active ACTV, read RD, pre-charge PRE, and deselect DSEL in synchronization with the first test clock WBI-CLK1. Concomitantly with this, the test address WBI-ADD is sequentially incremented from A0 in synchronization with the second test clock WBI-CLK2, which is obtained by frequency division of clock I-CLK to 1/4. Also, for the test data WBI-DATA, the data written in third mode MODE3 is generated as expected value. Since, in the fourth mode MODE4, only the read operation is performed, the read enable signal $\emptyset\text{RENB}$ stays at H level, and the third test clock WBI-CLK3 that is supplied to serial/parallel conversion circuit 34 and WBI output buffer

36 stay at L level.

In the case of the output mode OUTPUT shown in Figure 11, the third test clock WBI-CLK3 synchronized with clock I-CLK is generated after three clock cycles after the output mode signal OUTPUT becomes H level, causing the parallel/serial conversion circuit 34 and WBI output buffer 36 to operate synchronously therewith, so that the count value of failed bit counter 32 is serially output.

Figure 12 is a circuit diagram of the WBI control circuit. In response to the test operation mode signal ϕ MODE from WBI mode selector circuit 22, WBI control circuit 24 generates test mode start signal ϕ START, first test clock WBI-CLK1 for command generation, second test clock WBI-CLK2 for address/data generation, third test clock WBI-CLK3 for test result output, read enable signal ϕ RENB, and comparison timing signal ϕ COMP, which is the timing for data comparison.

In the first mode MODE1, as shown in Figure 7, the test mode start signal ϕ START becomes H level in response to the mode signal MODE1, first test clock WBI-CLK1 is generated in synchronization with the clock I-CLK, and second test clock WBI-CLK2 is generated by frequency division of clock I-CLK to 1/4.

When the first mode signal MODE 1 becomes H level, the output of NOR gate 71 becomes L level, and the test mode start signal ϕ START becomes H level through inverter 72. The H level of this start signal ϕ START is latched by

flip-flop 73, so that the output Q of flip-flop 73 becomes H level. Consequently, thereafter, first test clock WBI-CLK 1 is generated synchronized with internal clock I-CLK. Also, the first test clock WBI-CLK 1 is output as second test clock WBI-CLK2 through selector 78 after being divided to 1/4 by a 1/4 frequency divider 76.

In the case of the first mode MODE1, since this is a write operation, the read enable signal ϕ RENB stays at L level. Consequently, the output of NAND gate 87 is held at H level, and the comparison timing signal ϕ COMP stays at L level.

In the second mode MODE2, as shown in Figure 8, the test mode start signal ϕ START becomes H level in response to the mode signal MODE2, the first test clock WBI-CLK 1 is generated in synchronization with the clock I-CLK, and second test clock WBI-CLK2 obtained by frequency division to 1/8 of clock I-CLK is generated, also, the read enable signal ϕ RENB becomes H level with the read timing, and the comparison timing signal ϕ COMP also becomes H level.

When the second mode signal MODE2 becomes H level, the mode start signal ϕ START becomes H level through NOR gate 71 and inverter 72, causing first test clock WBI-CLK 1 to be generated. Since the second mode signal MODE2 is H level, the H level selector signal S80 is supplied to selector 78 through NOR gate 79 and inverter 80, causing node N2 to be selected; second test clock WBI-CLK2 obtained by frequency division to 1/8 of first test clock WBI-CLK

1 is generated by 1/4 frequency divider 76 and 1/2 frequency divider 77.

Then, through NAND gate 81 and 83, the read enable signal ϕ RENB also becomes H level, in synchronization with the second test clock WBI-CLK2 (utilizing the signal of node N2). Furthermore, when the read enable signal ϕ RENB is H level, a pulse synchronized with the trailing edge of internal clock I-CLK is output as comparison timing signal ϕ COMP through flip-flop 84 having a 1/2 frequency dividing function, inverter 85 and NOR gate 86 that generate a pulse on the trailing edge, NAND gate 87 and inverter 88.

In the case of the third mode MODE3, WBI control circuit 24 performs the same operation as in the case of the second mode MODE2.

In the case of the fourth mode MODE4, as shown in Figure 10, the test mode start signal ϕ START becomes H level in response to mode signal MODE4, causing the first test clock WBI-CLK1 to be generated in synchronization with the clock I-CLK and second test clock WBI-CLK2 to be generated by frequency division to 1/4 of clock I-CLK.

When the fourth mode signal MODE4 becomes H level, the output of NOR gate 71 becomes L level, and the test mode start signal ϕ START becomes H level through inverter 72. The H level of this start signal ϕ START is latched in flip-flop 73, with the result that the output Q of flip-flop 73 becomes H level. Consequently, thereafter, first test clock WBI-CLK1 is generated synchronized with the internal

clock I-CLK. Also, the first test clock WBI-CLK 1 is output
as the second test clock WBI-CLK2 through selector 78 by
frequency division to 1/4 by a 1/4 frequency divider. The
fourth mode signal MODE4 is H level, so the read enable
5 signal ϕ RENB is maintained at H level through inverter 82
and NAND gate 83. Concurrently, the comparison timing
signal ϕ COMP is output at every second clock pulse of
internal clock I-CLK.

In the output mode OUTPUT, the mode signal OUTPUT becomes
10 H level. This H level is obtained by flip-flops 90 and 91
in synchronization with the internal clock I-CLK.
Consequently, after the mode signal OUTPUT becomes H level,
node N3 becomes H level two clock pulses later, the output
of NAND gate 92 becomes L level, and node N4 becomes H level.
15 The H level of this node N4 is obtained by the flip-flop
94 in synchronization with the rising edge of the next
internal clock I-CLK, thereby causing generation of the
third test clock WBI-CLK 3 to be commenced.

That is, the operation of the WBI output buffer circuit
20 36 is delayed by a time t_1 shown in Figure 5 by these circuits.
Then, at this time t_1 , changeover of external terminal BISTZ
from input to output is performed. Also, with these circuits,
when the output mode signal OUTPUT drops to L level, this
is immediately detected by NAND gate 92, and at the rising
25 edge of the next internal clock I-CLK is stored in flip-flop
94, causing the generation of the third test clock WBI-CLK
3 to be stopped.

Figure 13 is a circuit diagram of the WBI command generating circuit. The WBI command generating circuit is a test operation command generating circuit that generates a test operation command WBI-CMD designating writing or reading and supplies this to memory control circuit 18. WBI command generating circuit 26 is provided with command sets 100 to 104 that respectively output signal sets (/CS, /RAS, /CAS, /WE) of active command ACTV, read command RD, write command WR, pre-charge command PRE, and deselect command DESEL, and also a switch control circuit 105 that successively selects a signal set from the set of these commands in synchronization with the rising edge of first test clock WBI-CLK1 whilst operation of mode start signal ϕ START is H level. Switches SW1 to SW4 are successively put in ON condition by the control signal from switch control circuit 105. Also, the selection of read command and write command is performed by a switch SW5 in accordance with the read enable signal ϕ RENB.

The test operation commands WBI-CMD indicated in Figure 7 to Figure 10 are generated in cyclic fashion synchronously with the first test clock WBI-CLK1, which is the clock for command generation, by this WBI command generating circuit 26. As shown in Figure 2, these test operation commands WBI-CMD are supplied to control circuit 18 of the memory circuit through selector 40.

Figure 14 is a circuit diagram of a test address/data generating circuit. Also, Figure 15 is an operation timing

chart of this test address/data generating circuit. In this
WBI address /data generating circuit 28, when test
operation mode start signal ϕ START becomes H level, the
reset signal S106 that is generated through inverter 106
5 becomes L level, causing operation of the binary counter
107 to be commenced. Specifically, binary counter 107
counts the second test clock WBI-CLK2 for test address and
test data generation. In the first and fourth test modes
MODE1, 4, this second test clock WBI-CLK2 is a clock obtained
10 by frequency division to 1/4 of the internal clock I-CLK
and, in the case of the second and third test modes MODE2,
3, is a clock obtained by frequency division to 1/8 of the
internal clock I-CLK.

Next, the count of this binary counter 107, or its
15 complement (inverted value) is output as the test address
WBI-ADD. The count value (a) and inverted value (b) of this
binary counter 107 are selected by the third mode signal
MODE3. That is, when the third mode signal MODE3 is H level,
the test address WBI-ADD must be decremented, so the
20 inverted value (b) is selected. In the case of the other
modes MODE1, 2, 4, the third mode signal MODE3 is L level,
and the uninverted value (a) is selected, the test address
WBI-ADD being incremented.

When the most significant bit MSB of binary counter
25 107 becomes 1, first test operation mode end signal END1
becomes H level.

Also, the least significant two bits of binary counter

107 are supplied to data generating circuit 109, to be utilized as the address for test data WBI-DATA generation. Specifically, as shown in Figure 6, for the test data WBI-DATA, a checkered pattern corresponding to the position of the memory cell is employed. To achieve this, the position of the memory cell in question must be recognized by the least significant two bits of the address.

Also, data generating circuit 109 must generate inverted test data WBI-DATA when in the second test mode MODE2 and in the third test mode MODE2. Moreover, in the first and fourth test modes MODE1, 4, it does not need to invert the test data. To achieve this, in the second mode MODE2, second test clock WBI-CLK2 inverted by inverter 110 is supplied to data generating circuit 109 from node N10 through NAND gates 112, 13. Also, in the case of the third mode MODE3, the second test clock WBI-CLK2 is supplied from node N10 to data generating circuit 109 through NAND gates 111, 113. Data generating circuit 109 generates checkered pattern test data WBI-DATA in accordance with node N10 and the least significant 2-bit test address. Figure 15C shows an example of this test data. "0110" and "1001" are the combinations of test data in respect of the word line WL and line BL. In order to apply the maximum stress to the memory unit as in the burn-in test, in view of the physical arrangement of the memory cells, data should be written in a checkerboard pattern as shown in the example of WBI data of Figure 15C.

It is to be understood that test commands WBI-CMD and test data WBI-DATA are generated so as to execute the four operating modes shown in Figure 7 to Figure 10 by the above test command generating circuit 26 and test address/data
5 generating circuit 28.

Figure 16 is a layout diagram of the data comparison unit, counter, parallel/serial conversion unit, and test output buffer. Figure 17 is an operation timing chart of the data comparison unit. In data comparison unit 30 a
10 comparison is effected in which the test data WBI-DATA and the data DOUT read from the memory cells are input to an exclusive OR circuit comprising gates 113 and 114. In this circuit example, the timing clock N13 for the comparison is generated from mode start signal ϕ START and comparison timing signal ϕ COMP. However, instead of the comparison timing signal ϕ COMP, the data transfer signal whereby the read data is transferred from database DB to data
15 input/output circuit DI/O in the memory circuit may be utilized.

20 If the result of the comparison by the exclusive OR circuit is non-coincidence, a fail signal ϕ F is generated, and this is counted by binary counter 32 constituting failed bit counter 32. This fail signal ϕ F is output synchronously with the control clock N12 delayed by delay circuit 115.

25 Binary counter 32 counts up the fail signal ϕ F and, when it overflows, all the count values are forcibly set to 1 by means of overflow signal OF. Further counting up

of the fail signal ϕF is then stopped. The count value of binary counter 32 is the number of times that failed bits are detected and constitutes the comparison result information of the self-test. Also, all of the count values being 1 constitutes the test result information that overflow has occurred. These count values are utilized in Weibull control in which the relationship between the burn-in stress time in the burn-in test and the number of failed bits is controlled.

In outputting these test results, all the bits of binary counter 32 are converted to serial data by the parallel/serial conversion circuit 34 and serially output from test output buffer 36 in synchronization with the third test clock WBI-CLK3, which is the output control clock. When serial output terminates, parallel/serial conversion circuit 34 generates a second end signal END2 indicating that the output mode operation has terminated.

The number of bits of failed bit counter 32 may be made equal to the maximum count value of the number of failures, corresponding to the maximum number of failed bits that can be rescued. This is because if this is exceeded, rescue by the redundant cells cannot be performed, so the device must be a failed device. Consequently, the test step itself may be discontinued once it has been ascertained that the maximum number of failures has been detected.

For example, in the case of the march pattern shown in Figure 6, if the test is performed solely for the

uninverted data, read data comparison is performed a total of three times. Consequently, the number of bits of failed bit counter 32 is chosen to be (maximum number of addresses that can be rescued by redundancy) X 3. Binary counter 32
5 outputs an overflow signal OF when this maximum number of bits is exceeded. That is, failed bit counter 32 may have a bit number of at least three times the maximum number that can be rescued (in the case where an inverted pattern is used, at least six times).

10 [Second embodiment]

Figure 18 is a layout diagram of a memory device according to a second embodiment. In the second embodiment, a clock multiplier circuit 120 is provided on the output side of clock input buffer 10; in the self-test step, a
15 clock CLK2 obtained by multiplying a comparatively slow clock I-CLK2 that is provided from outside is supplied to self-test circuit BIST and the interior of the device. Specifically, a clock CLK of for example 10 MHz is received from outside, and this is multiplied internally to 20 MHz,
20 to operate the internal circuitry at double speed. Also, in this case, interface with the outside is effected by supplying an unmultiplied clock I-CLK 1 to the input/output circuits 21, 36. Also, multiplied clock I-CLK2 could be of three times the speed or four times the speed of external
25 clock CLK.

The rest of the construction is the same as in the case of the first embodiment shown in Figure 2. By the provision

of a clock multiplier circuit 120 as described above, this self-test can be performed with an inexpensive tester of low clock frequency. For the clock multiplier circuit 120, for example a construction using a DLL circuit may be employed. Alternatively, another generally used circuit layout may be employed.

[Third embodiment]

Figure 19 is a layout diagram of a memory device incorporating a self-test circuit according to a third embodiment. The third embodiment is an example in which the testing can be carried out using the self-test circuit BIST also after assembly into the form of a package. To achieve this, in WBI activation circuit 20, in addition to the activation signal WBIZ in the wafer level burn-in test, a second activation signal WBIZ2 is additionally input from a test mode selection circuit 126 that selects test mode with a special command. When either of these activation signals WBIZ or WBIZ2 is in active condition, WBI activation circuit 20 detects that the self-test step is being performed and makes the internal WBI activation signal ϕ WBI of H level.

Test mode selector circuit 126 generates the second activation signal WBIZ2 when a specific combination of external command input CMD and/or address input A0 to Am is input. Therefore, self-test circuit BIST is activated in response to the activation signal WBIZ in the wafer condition in the same way as in the first embodiment and,

after assembly, is activated in response to a specific combination of command input CMD and address signal.

An example circuit of the WBI activation circuit corresponding to the third embodiment is shown in the bottom left-hand part of Figure 3. The internal WBI activation signal ϕ WBI becomes H level in response to either of the two activation signals WBIZ, WBIZ2 becoming H level.

In the third embodiment, in addition, there is provided a selector 43 whereby the output of parallel/serial conversion circuit 33 is output to the outside sharing the I/O buffer of the memory device. Consequently, the input/output terminal DQ0, in the ordinary operation condition, functions as an input/output terminal, and, in the self-test step, functions as an output terminal that outputs the test result information constituted by the value of counter 32. In this way, in the self-test step utilizing the self-test circuit BIST, the activation signal terminal WBIZ is only utilized in a special way in the wafer level burn-in test. The number of probes onto the wafer can therefore be further restricted.

[Fourth embodiment]

Figure 20 is a layout diagram of a WBI activation circuit and WBI mode selector circuit according to a fourth embodiment. The WBI mode selector circuit in the fourth embodiment is a modification of that of Figure 3. The WBI mode selector circuit 22 shown in Figure 20 is provided with flip-flops 134 to 138. These flip-flops input as

set/reset signal the pulse generated by pulse generating circuit 130 at the rising edge of WBI activation signal \emptyset WBI, and input as data input clock the pulse generated by pulse generating circuit 132 at the rising edge of one or other of the operation mode termination signals END1, 2.

Consequently, when the WBI activation signal \emptyset WBI becomes H level, the flip-flops 134 to 138 sequentially automatically generate test mode signals MODE1 \rightarrow MODE2 \rightarrow MODE3 \rightarrow MODE4 \rightarrow OUTPUT. By utilizing this WBI mode selector circuit, input of the mode signal BISTZ as shown in Figure 2 or 3 is unnecessary, so the self-test can be executed in an even simpler fashion.

[Fifth embodiment]

Figure 21 is a view showing an example of a test result information output unit according to a fifth embodiment. Two examples are shown in Figure 21. As output unit, self-test circuit BIST comprises a comparison result accumulation circuit that accumulates the data comparison result information in some form, and a test output circuit that outputs this comparison result information. In the first embodiment shown in Figure 2, there are provided a fail bit counter 32, parallel/serial conversion circuit 34, and test output buffer 36, and the count value of counter 32 or the information of its overflow condition is output.

The output unit of Figure 21A comprises a binary counter 32 that is supplied, as fail signal \emptyset F, with comparison

result information indicating that the result of the data comparison was non-coincidence, and that accumulates the number of times this occurs; and an output circuit 142 that outputs an overflow signal OF generated when this binary counter 32 overflows. Consequently, only information as to whether or not overflow occurred is output. Consequently, this output unit can be utilized when it is sufficient to determine whether the chip is a chip that can be rescued by redundant cells of the memory circuit or a chip that cannot be thus rescued.

In the example of Figure 21A, the overflow signal OF is initially L level. When fail signals $\emptyset F$ are generated in excess of the number that can be accommodated by redundancy, the overflow signal OF becomes H level, and input of fail signals $\emptyset F$ is stopped by circuit 140. If, thereafter, an output control signal $\emptyset OUT$ is input, output circuit 142 outputs the overflow signal OF. The binary counter 32 is set by generation of the reset signal S141 consisting of the output control signal $\emptyset OUT$ delayed by one clock pulse by delay circuit 141.

The example output unit of Figure 21B is of a construction that outputs as comparison result information three types of identification information, namely, passed chip in which redundant cells do not need to be used, chip that can be rescued by means of the redundant cells, and chip that cannot be rescued by the redundant cells. Even if the fail signal $\emptyset F$ is generated only once, first bit

B1 of register 146 is made H level through NOR gate 144 and inverter 145. Also, when binary counter 32 overflows, the second bit B0 of register 146 becomes H level. The first bit B1 therefore provides the information as to whether the chip is a passed chip with no defect or whether it is a chip that does have a defect but can be rescued by the means of the redundant cells. The second bit B2 provides the information as to whether the chip is or is not a defective chip that cannot be rescued by the redundant cells. Output circuit 148 sequentially serially outputs this test result information of the two bits B0, B1 of the register 146 for example in response to output control signal ϕ OUT. If the output is (B0, B1)=(0, 0), it is concluded that the chip is a passed chip, if it is (0, 1), it is concluded that the chip is a chip that is capable of being rescued by redundancy, and if it is (1, 1) it is concluded that the chip is incapable of redundancy.

The output circuit shown in Figure 21 cannot output the number of failed bits as comparison result information, but its circuit layout is correspondingly simplified. Also, it is not necessarily essential for the third test clock WBI-CLK3 to be employed for the output control circuit; any sort of pulse signal can be employed.

[Sixth embodiment]

Figure 22 is a layout diagram of a memory device according to a sixth embodiment. If the WBI activation circuit and WBI mode selector circuit (Figure 20) in the

fourth embodiment and the data output circuit (Figure 21) in the fifth embodiment are employed, the interface with the outside does not require a clock. Accordingly, in the sixth embodiment, utilizing these circuits, there is
5 incorporated, in addition, an oscillator OSC that is activated during self-test operation. In addition, there is provided a selector 150 that is changed over to the clock generated by oscillator OSC from the external clock CLK during self-test operation.

10 In the sixth embodiment, when activation signal WBIZ is applied, oscillator OSC starts generation of the clock signal, and supplies this through selector 150 to the memory circuit and/or other circuits. Also, WBI mode selector circuit 22 generates sequential mode signal ϕ MODE, and,
15 in accordance therewith, the tests of the respective modes are executed, and the test results are output from input/output terminal BISTZ for self-test. Consequently, in this case, the test costs can be further reduced since no external clock signal is necessary.

20 In the foregoing embodiments, the self-test circuit was described under the assumption that it would be utilized in a wafer level burn-in test. However, this self-test circuit could also be utilized in a burn-in test at package level after assembly. In the case of both tests, the presence
25 of failed bits can be detected by the memory device itself performing an internal test simply by supplying an external activation signal and/or mode input signal etc.

In addition, the test operation commands of the above
embodiments were for the case of SDRAM or FCRAM; in the
case of memory devices of other types, the operation
commands employed for these are generated as test operation
5 commands.

[Seventh embodiment]

In the first, second, third and six embodiments
described with reference to Figure 2, 18, 19, 22, selector
40 for performing changeover between the external command
10 CMD and a test operation command WBI-CMD, selector 41 for
performing changeover between the external address EXADD
and test address WBI-ADD, and selector 42 for performing
changeover between the write input data DIN and test data
WBI-DATA are provided between the respective input circuit
15 and the memory bank MBNK.

The burn-in test is a test which is conducted in order
to exclude devices having initial defects, by applying
stress to the device. It is therefore desirable that as
many circuits as possible should be made to operate in the
20 burn-in test. Consequently, so far as the address, command
and data input circuits are concerned, the number of
circuits that are made to operate under stress during the
burn-in test can be made larger by adopting a construction
in which the test address WBI-ADD, test operating command
25 WBI-CMD and test data WBI-DATA generated by the self-test
circuit BIST are input from as close as possible to the
external input terminal.

Consequently, in the seventh embodiment, the selectors are arranged close to the external input terminal. However, if such a selector circuit were directly connected to the input terminal, there would be adverse effects such as an increase in input terminal capacitance. Accordingly, the selector is provided in an input circuit. In a specific example, the selector is provided between the input buffer and latch circuit of an input circuit.

Figure 23 is a view showing the construction of an input circuit according to a seventh embodiment. Describing the construction of Figure 23 by comparison with the third embodiment illustrated in Figure 19, the address input circuit 14 constituting the address buffer comprises an input buffer 14A connected to an external terminal and that inputs signals from outside and subjects these to waveform shaping and/or voltage level conversion, and a latch circuit 14B that latches the output of input buffer 14A in synchronization with the rising edge of clock I-CLK. A selector 41 that effects changeover in response to a start signal ϕ START generated by the self-test circuit BIST is provided between input buffer 14A and latch circuit 14B. Although not shown in Figure 23, the command input circuit 11 and data input circuit 13 in front of the command decoder 12 likewise have a selector provided in front of the latch circuit.

Taking the example of address input circuit 14, input buffer 14A is constituted for example by a current mirror

circuit and is provided with an amplification function and/or a function of level conversion to an internal power source. Also, during normal operation, the latch circuit latches the externally supplied addresses A0 to Am in
5 synchronization with the rising edge of clock I-CLK and, during self-test, latches the test address WBI-ADD from self-test circuit BIST in synchronization with the rising edge of clock I-CLK. Command input circuit 11 and data input circuit 13 also operate in the same way.

10 By adopting such a construction, during self-test, the operation of the internal circuitry downstream of latch circuit 14B can be made the subject of a stress test, making it possible to perform a more accurate burn-in test.

15 However, if selector circuits are provided in this way in the vicinity of the input terminal, the following two problems arise. Firstly, since there is a latch circuit that effects latching in synchronization with the clock I-CLK downstream of the selector circuit, the timing with which the test address WBI-ADD, test operation command
20 WBI-CMD, and test data WBI-DATA generated by the self-test circuit BIST are generated must be matched with the timing of the latch of the input circuit. Secondly, when there is provided a function of performing a burn-in test by activating the self-test circuit BIST by an external
25 command after assembly into the form of a package described in the third embodiment of Figure 23, since, in normal operation, if self-test mode is accidentally entered, the

selector circuit is changed over to the test side, it becomes impossible to input a self-test cancellation command from the external command terminal.

The first problem described above can be solved by providing an inverter 15 that generates a second internal clock I-CLK2 obtained by inverting the internal clock I-CLK, as shown in Figure 23. The second internal clock ICLK2 is advanced in phase by 180° with respect to the internal clock I-CLK that controls the latch timing. Consequently, the self-test circuit BIST can generate test address WBI-ADD, test operation command WBI-CMD and test data WBI-DATA at the rising edge of the second internal clock I-CLK2 and the latch circuit 14B can latch the signal that is changed over by the selector in synchronization with the rising edge of the subsequent internal clock I-CLK.

Figure 24 is a timing chart illustrating the relation of generation and input of the test address etc. The device gets the external signals in synchronization with the clock I-CLK, so input signals such as the test address etc must be supplied to the internal circuitry with a timing whereby the set-up time and hold time are guaranteed with respect to this internal clock I-CLK. In order to achieve this, an inverted clock I-CLK2 is generated by inverter 15, and self-test circuit BIST is arranged to operate in synchronization with the down edge of the internal clock I-CLK. That is, since self-test circuit BIST generates and supplies the test address etc in synchronization with the

down edge of the internal clock I-CLK, latch circuit 14B can latch the test address etc in synchronization with the up edge of the next internal clock I-CLK.

In this example, the second internal clock I-CLK2 was an inverted clock obtained from internal clock I-CLK, but it would be possible to use a clock which was obtained by advancing internal clock I-CLK by a prescribed time as the second internal clock I-CLK2. However, if an inverted clock is employed, it suffices merely to provide an inverter and this is thus simplest in circuit terms.

Regarding the second problem, when selector circuit 41 etc is changed over to the self-test side by putting the internal circuitry in self-test mode in response to input of a self-test entry command as an external command, it is necessary to arrange that the self-test cancellation command can be input as an external command. To achieve this, the self-test circuit BIST temporarily makes the start signal \emptyset START that changes over selector circuit 41 become L level in response to one or other of the input terminals or a combination of input terminals. As a result, the selector circuit 41 is changed over to the external terminal side by the L level of the start signal \emptyset START, making it possible to input a prescribed self-test cancellation command from outside.

This second problem arises when the self-test circuit BIST is utilized in a burn-in test after assembly into a package. Even if a self-test entry command is accidentally

input during normal operation, by making it possible to
input a self-test cancellation command at least from
outside by changing over the selector circuit by means of
one or other of the input terminals or a combination of
5 input terminals, the second problem can be solved.

In the example illustrated in Figure 23, external
address Am is utilized as the self-test cancellation
terminal. In the self-test circuit BIST, as shown also in
Figure 19, there is provided a WBI activation circuit 20
10 that generates a WBI activation signal ϕ WBI in response
to one or other of activation signal WBIZ and second WBIZ2.
As shown in Figure 3, WBI activation circuit 20 puts the
WBI activation signal ϕ WBI in H level test mode in response
to the H level activation signal WBIZ that is input from
15 a special external terminal WBIZ employed in the wafer level
burn-in test. Also, the activation signal ϕ WBI becomes L
level when the external terminal WBIZ becomes open, with
the result that the WBI activation signal ϕ WBI becomes the
L level normal mode.

20 In contrast, after the assembly step, the second
activation signal WBIZ2 is made H level by an entry command
from outside, so, when the external address Am becomes H
level, the WBI activation signal ϕ WBI becomes H level, and
self-test mode is entered. Then, when the external address
25 Am becomes L level, the WBI activation signal ϕ WBI
temporarily becomes L level, the start signal ϕ START
becomes L level, and a condition in which signal input from

outside is possible is produced. The normal mode can then be returned to by the second activation signal WBIZ2 becoming L level in response to input of a self-test cancellation command from outside.

5 Address terminal Am may be a terminal that is not required for the command for entering self-test mode. The terminal for temporarily canceling self-test mode may therefore be a command terminal or DQ terminal. Thus, in self-test mode, the self-test circuit BIST is operated by making address Am="H", but, by making address Am="L", the self-test circuit BIST is disabled so that address and command can be input from outside.

10 Figure 25 is a timing chart to illustrating entry and cancellation of self-test mode after assembly. Also, Figure 26 is a circuit diagram of the WBI activation circuit 20 for achieving this. Entry and cancellation of self-test mode in the wafer condition and entry and cancellation of self-test mode after assembly will be described with reference to these Figures.

15 In the wafer condition, when an H level activation signal WBIZ is input from test terminal WBIZ, the output of inverter 200 becomes L level and the output of inverter 201 becomes H level. The output N100 of NAND gate 204 thereby becomes H level, so causing transistor 208 to become conductive while the transistor 207 becomes non-conductive, and node N102 to be maintained at L level irrespective of the address Am. Consequently, both inputs of NOR gate 203 become L level,

and the WBI activation signal \emptyset WBI becomes H level, causing the self-test mode to be entered. Consequently, the signal of address Am is ignored. Thus, when the signal of test terminal WBIZ is made L level, the WBI activation signal \emptyset WBI becomes L level, and the self-test mode is canceled. Thus, in the wafer condition, entry and cancellation of the self-test mode are performed solely by means of test terminal WBIZ.

Next, after assembly, when an entry command is input from the external address terminal or command terminal, the second activation signal WBIZ2 becomes H level. At this point, the test terminal WBIZ is in the open condition and is fixed at L level. Consequently, the H level output of inverter 200 and the second activation signal WBIZ2 are input to NAND gate 204 thereby making node N100 L level, as a result of which transistor 207 is maintained conductive while transistor 208 is maintained non-conductive, and the inverted signal of address Am is output to node N102. If Am is H level, node N102 becomes L level, and the output of NOR gate 203 becomes H level. That is, the WBI activation signal \emptyset WBI is controlled to H level by address Am, causing self-test mode to be entered.

In order to cancel the self-test mode, address Am is made L level. Node N102 thereby becomes H level, and WBI activation signal \emptyset WBI becomes L level. In response to this, self-test circuit BIST makes start signal \emptyset START L level, and changes over the selector circuit to the input terminal

side. A condition in which an external command can be input is thereby produced. Thereupon, when a self-test cancel command is input from outside, the second activation signal WBIZ2 is made L level by test mode selection circuit 126, producing the normal mode. Thereafter, the input of address Am is ignored, and the normal mode is maintained.

Although, in the above example, a single address terminal Am delivers input to self-test circuit BIST as a self-test mode halt signal, it would be possible to create a self-test mode halt signal by decoding the signals of a plurality of address terminals and/or command terminals. If it is arranged for this halt signal to be generated by a combination of inputs of self-test mode cancellation commands, when the self-test mode cancellation commands are input from outside, the start signal ϕ START becomes L level and the cancellation commands are input to the device, causing the self test mode to be canceled.

Also, when the present invention is applied to DRAMS etc, in order to achieve automatic cancellation when this self-test mode is entered by mistake in the normal use condition, the "pre-charge" command in which a selected memory bank is pre-charged and/or the "pre-charge all" command in which all the memory banks are pre-charged could be used as a self-test mode cancellation command. As a result, an accidentally entered self-test mode can be canceled by a pre-charge command, thereby making it possible to shift to the next operating cycle in a suitable manner.

Figure 27 is a further input circuit layout diagram according to a seventh embodiment. Figure 28 is a timing chart illustrating entry and cancellation of self-test mode after assembly in the case of Figure 27. In this example, the start signal \emptyset START is input through a switch SW10 to a selector 41 of the input circuit. Also, this switch SW10 is controlled by an input signal A0. When address A0 is maintained at H level, the start signal \emptyset START continues to be supplied to selector 41; when address A0 is made L level, the switch SW10 is turned off, causing an L level start signal to be supplied to selector 41, as a result of which it goes into a condition in which an external command can be input.

For example, switch SW10 may be constituted by an AND gate as shown in Figure 27. After self-test mode is entered, if H level is applied to input terminal A0, the start signal \emptyset START continues to be input to selector 41, with the result that the signal generated by self-test circuit BIST such as a test address is input by the input circuit. If L level is applied to input terminal A0, the start signal \emptyset START is cut off, and an input signal A0 from outside is input to selector 41.

This switch SW10 is provided at a terminal that inputs the self-test mode cancellation command. And the self-test mode cancellation command comprises such a terminal L level. In this way, in this self-test mode, during activation of the self-test circuit BIST, these terminals are made H level,

but, when the self-test mode is to be canceled, as a cancellation command, these terminals are made L level, causing the self-test mode cancellation command to be input to the device, thereby canceling the self-test mode.

5 Switches SW10 need not be provided at all terminals. Also, the switches SW10 of a plurality of terminals may be controlled by the input signal of a single terminal. Also, when, as described above, this embodiment is applied to a DRAM etc, in order to cancel an erroneously entered
10 self-test mode in the normal use condition, the pre-charge command may be used as a self-test mode cancellation command.

In this embodiment, when a self-test mode cancellation command is input, switch SW10 is turned off by L level of
15 the prescribed terminal (in the example of Figure 27, address A0) contained in this command, and all of the selectors with which the switch is provided are changed over to the external input terminal side. As a result, this cancellation command is input, test mode selector circuit
20 126 makes the second activation signal WBIZ2 L level, and the self-test mode of self-test circuit BIST is canceled. As a result, start signal ϕ START is made L level, producing the normal mode.

Also, when self-test mode is entered, the selector
25 changes over to the input terminal side, so the entry command is input into the device, causing test mode selector circuit 126 to make second activation signal WBIZ2 H level, and

to make start signal ϕ START H level.

Hereinabove, in the seventh embodiment, the test address WBI-ADD, test operation command WBI-CMD and test data WBI-DATA that are generated by the self-test circuit BIST can be supplied from a circuit that is as close as possible to the input terminal. Consequently, the test can be conducted in a more precise condition. Also, even if the self-test mode is entered by mistake in the normal condition, the selector can be forcibly changed over to the input terminal side, so that this self-test mode can be canceled.

[Eighth Embodiment]

The eighth embodiment relates to the reset operation in self-test mode. In a device such as a DRAM, there are provided a large number of latch circuits such as flip-flops in the interior. Consequently, there is provided a function of resetting these latch circuits in response to a reset command from outside or on connection of the power source. In the same way, even in self-test mode, a function of resetting the internal circuitry is needed. In this embodiment, a reset function is implemented in the self-test mode.

Figure 29 is a view given in explanation of the reset function in the eighth embodiment. Figure 29A is a layout diagram of the entire device, illustrating a main circuit 300 of the memory that includes memory banks and/or control circuitry etc, a self-test circuit BIST, and a reset signal

generating circuit 305 that supplies these reset signals
RESET1, 2, 3. Also, Figure 29B shows reset signal generating
circuit 305 and Figure 29C shows a table illustrating the
relationship between the reset request signals S1, S2, S3
5 and reset signals RESET1, 2, 3.

Start circuit 304 generates a first reset request signal
S1 in response to connection of power source VDD. In response
to this, reset signal generating circuit 305 generates a
first reset signal RESET1 for main circuit 300 excluding
10 command decoder 302, a second reset signal RESET2 for
command decoder 302, and a third reset signal RESET3 for
self-test circuit BIST. As a result, the latch circuits
incorporated in main circuit 300, command decoder 302
and self-test circuit BIST are reset.

15 When a forcible reset command is input from outside,
secondary reset request signal S2 is generated as a forcible
reset signal by command decoder 302. In response to this,
reset signal generating circuit 305 generates a first reset
signal RESET1 for main circuit in 300 excluding command
20 decoder 302 and a third reset signal RESET3 for self-test
circuit BIST. As a result, the latch circuits incorporated
in main circuit 300 and self-test circuit BIST are reset.
However, the command decoder 302 that outputs the second
reset request signal S2 is not reset.

25 When a reset command is serially input from the test
terminal WBIZ that is employed for the self-test at wafer
level, self-test circuit BIST generates third reset request

signal S3. In response to this, reset signal generating circuit 305 generates first reset signal RESET1 for main circuit 300 and reset signal RESET2 for command decoder 302. As a result, the latch circuit incorporated in main circuit 300 and/or command decoder 302 are reset. In this case, no third reset signal RESET3 is generated. As a result, the self-test circuit BIST is not reset, and the third reset request signal S3 is held, so that reset of main circuit 300 is correctly performed.

Figure 30 is a view showing a WBI mode selector circuit that generates a reset request signal S3 in response to a serial command from test terminal WBIZ. Since Figure 30 is a modified example of Figure 3, the same reference numerals are employed. The circuit layout of Figure 30 is the same as that of Figure 3. However, when a reset command is serially input from test terminal WBIZ, decoder 58 generates reset request signal S3 as a fifth WBI mode select signal. In response to this reset request signal S3, the reset signal generating circuit 305 shown in Figure 29 generates a reset signal RESET1 for main circuit 300.

In the above, according to the present invention, instead of employing an LSI tester, a self-test circuit incorporated in the memory device can perform checking for failed bits by being supplied with a self-test activation signal from outside. Consequently, the time required for the test step can be shortened compared with a conventional memory device.

Also, according to the present invention, even in a burn-in test in which a small number of external terminals are utilized in the wafer step, a self-test can be performed by utilizing the incorporated self-test circuit, thereby contributing to lowering the costs of the device.

The scope of protection of the present invention above is not restricted to the above embodiments but extends to the invention as set out in the claims and equivalents thereof.

What Is Claimed Is:

1. A self-test circuit that detects defects of a memory device, incorporated in the memory device having a memory control circuit that controls write and read operations
5 with respect to a memory core in response to a command, comprising:

a test operation command generating circuit that, in self-test activated condition, generates a test operation command that designates said writing or reading, and that
10 supplies the test operation command to said memory control circuit;

a test address generating circuit that, in said self-test activated condition, generates a test address and supplies the test address to said memory core;

15 a test data generating circuit that, in said self-test activated condition, generates test data and supplies the test data to said memory core; and

a test output circuit that compares read data from said memory core with said test data and stores information as
20 to the result of this comparison, and outputs the information to the outside;

wherein said self-test circuit goes into the self-test activated condition in response to a self-test activation signal from outside.

25 2. The memory device self-test circuit of claim 1 further comprising a test operation mode selector circuit that,

in said self-test activated condition, generates a test operation mode signal that designates any of a plurality of test operation modes including said write and/or read,

wherein, in response to said test operation mode signal,
5 said test operation command generating circuit generates said test operation command for executing said test operation mode.

3. The memory device self-test circuit of claim 2 wherein
10 said test operation mode selector circuit generates said test operation mode signal by decoding a plurality of test operation mode input signals supplied from outside.

4. The memory device self-test circuit of claim 3 wherein
15 said plurality of test operation mode input signals are serially input in synchronization with an input timing signal.

5. The memory device self-test circuit of claim 2 wherein
20 said test operation mode selector circuit sequentially generates said plurality of test operation mode signals in said test activation condition.

6. The memory device self-test circuit of claim 1 wherein
25 the self-test activation signal is one or other of a signal supplied from a self-test input terminal or a signal generated in response to a prescribed command of said memory

device.

7. The memory device self-test circuit of claim 6 wherein
said self-test input terminal is maintained at a prescribed
5 potential in the open condition.

8. The memory device self-test circuit of claim 1 wherein
said test operation command generating circuit
sequentially generates a plurality of test operation
10 commands corresponding to operations including at least
one of said write or read, every time a particular address
is generated by said test address generating circuit.

9. The memory device self-test circuit of claim 1 wherein
15 said test address generating circuit comprises an address
counter and said test address is generated by counting an
address timing signal for address incrementing or
decrementing.

20 10. The memory device self-test circuit of claim 9
wherein said address counter of the test address generating
circuit selectively outputs a non-inverted output or
inverted output of the counter value, in accordance with
said test operation mode signal.

25 11. The memory device self-test circuit of claim 1
wherein, when said test operation command corresponds to

write operation, said test data generating circuit supplies
the test data to said memory core as write data and, when
said test operation command corresponds to read operation,
said test data generating circuit supplies the test data
5 to said test output circuit as comparison data.

12. The memory device self-test circuit of claim 11
wherein said test data generating circuit generates said
test data in a prescribed pattern in accordance with said
10 test address signal in synchronization with said address
timing signal.

13. The memory device self-test circuit of claim 1
wherein said test output circuit comprises a counter that
counts the number of times of non-coincidence of said read
15 data and the test data.

14. The memory device self-test circuit of claim 13
wherein the counter of said test output circuit has as its
20 maximum count value a number of times of said
non-coincidence corresponding to at least the maximum
number of failed bits that can be rescued.

15. The memory device self-test circuit of claim 14
25 wherein the counter of said test output circuit generates
an overflow signal when its count value exceeds said maximum
count value, and outputs the fact that the overflow has

occurred.

16. The memory device self-test circuit of claim 1
wherein said test output circuit comprises a
5 parallel/serial conversion circuit and serially outputs
said comparison result information in synchronization with
an output timing signal.

17. The memory device self-test circuit of claim 1
10 wherein said test output circuit outputs, as said
comparison result information, information as to whether
or not the number of times of non-coincidence of said read
data and test data is equal to or below the number of times
that can be rescued.

18. The memory device self-test circuit of claim 17
wherein said test output circuit further outputs, as said
comparison result information, information that
non-coincidence of said read data and test data did not
20 occur.

19. The memory device self-test circuit of claim 17
wherein said test output circuit further outputs, as said
comparison result information, the number of times of said
25 non-coincidence.

20. The memory device self-test circuit of claim 4

wherein said input timing signal is a test clock signal that is generated based on a clock supplied from outside.

21. The memory device self-test circuit of claim 8 wherein said test operation command generating circuit generates said test operation command in synchronization with a command generation timing signal that is generated from a clock supplied from outside.

22. The memory device self-test circuit of claim 9 wherein said address timing signal is a test clock signal that is generated from a clock supplied from outside.

23. The memory device self-test circuit of claim 16 wherein said output timing signal is a test clock signal that is generated from a clock supplied from outside.

24. The memory device self-test circuit of claim 20, 21, 22 or 23 further comprising a clock multiplication circuit that generates an internally generated clock by multiplying said clock supplied from outside and

wherein said timing signal is generated from the internally generated clock.

25. The memory device self-test circuit of either of claim 21 or 22 further comprising an oscillator that generates an internally generated clock in the self-test

activated condition, and wherein said timing signal is generated from the internally generated clock.

26. A memory device including a memory core having a plurality of memory cells and a memory control circuit that controls write and read operations in respect of said memory core in response to an external command, in which writing or reading of said memory cells corresponding to an external address is performed, said memory device comprising:

a self-test circuit that detects defects of said memory device by assuming a self-test activated condition in response to a self-test activation signal from outside;

wherein said self-test circuit comprises:

a test operation command generating circuit that, in said test activated condition, generates a test operation command that designates said writing or reading and supplies the test operation command to said memory control circuit;

a test address generating circuit that, in said self-test activated condition, generates a test address and supplies the test address to said memory core;

a test data generating circuit that, in said self test activated condition, generates test data and supplies the test data as write data to said memory core; and

a test output circuit that compares the read data from said memory core with said test data and stores the comparison result information.

27. The memory device of claim 26 comprising:
a first selector that changes over said external command
and said test command;
5 a second selector that changes over said external
address and said test address; and
a third selector that changes over external write data
supplied from outside and said test data.

10 28. The memory device of claim 27 further comprising:
a clock multiplier circuit that generates an internally
generated clock by multiplying an external clock supplied
from outside; and
a fourth selector that changes over said external clock
15 and said internally generated clock.

29. The memory device of claim 27 further comprising:
an oscillator that generates an internally generated
clock in the self-test activated condition; and
20 a fourth selector that changes over said external clock
and said internally generated clock.

30. The memory device of claim 27 further comprising:
a data output circuit that outputs read data that is
25 read from said memory cells; and
a fifth selector that changes over the comparison result
information from said test output circuit and said read

data and supplies this to said data output circuit.

31. The memory device of claim 26, further comprising
a self-test external terminal that is supplied with said
5 self-test activation signal.

32. The memory device of claim 26 wherein said self-test
activation signal is supplied by a prescribed external
command.

33. The memory device of claim 27 wherein at least one
of said first, second and third selectors is provided at
a corresponding input circuit, and

said input circuit inputs an input signal that is changed
15 over by said selector in synchronization with a first clock
and said self-test circuit supplies to said selector a
corresponding signal from among said test command, test
address, or test data in synchronization with a second clock
which is advanced in phase from said first clock.

34. The memory device of claim 33 wherein said input
circuit comprises an input buffer that inputs an external
command, external address, and/or external write data, and
a latch circuit that latches the output of said input buffer,
25 at least one of said first, second and third selectors being
provided between said input buffer and latch circuit.

35. The memory device of claim 33 wherein said input circuit inputs said input signal in synchronization with one edge of the clock and said self-test circuit generates said corresponding signal in synchronization with the other edge of said clock.

36. The memory device of claim 33 wherein said self-test activation signal is one or other of a signal supplied from a self-test input terminal or a signal generated in response to a prescribed external command of said memory device, and

in self-test mode, at least some of said selectors are changed over to the external input terminal side in response to a condition of a prescribed external terminal.

37. The memory device of claim 26 wherein a reset signal is supplied to the internal circuitry which includes at least said memory core and memory control circuit, in response to a reset command supplied from a self-test input terminal, and said internal circuit is reset.

38. A memory device comprising:

a memory core having a plurality of memory cells;

a memory control circuit that controls write and read operations to said memory core in response to an external command, in which writing or reading is performed to said memory cells corresponding to an external address;

ABSTRACT

The present invention is a self-test circuit(BIST) incorporated in the memory device, which is activated in response to a test activation signal from outside. When
5 this self-test circuit is activated in response to a test activation signal(WBIZ) from outside, it generates a test operation command(WBI-CMD), generates a test address(WBI-ADD), and generates test data(WBI-DATA). Furthermore, after the self-test circuit writes the test
10 data to a memory cell, it effects a comparison to establish whether or not the read data that is read from this memory cell is the same as the test data that was written thereto and stores information as to the result of this comparison. This comparison result information is then output to the
15 outside.

FIG. 1

Prior Art

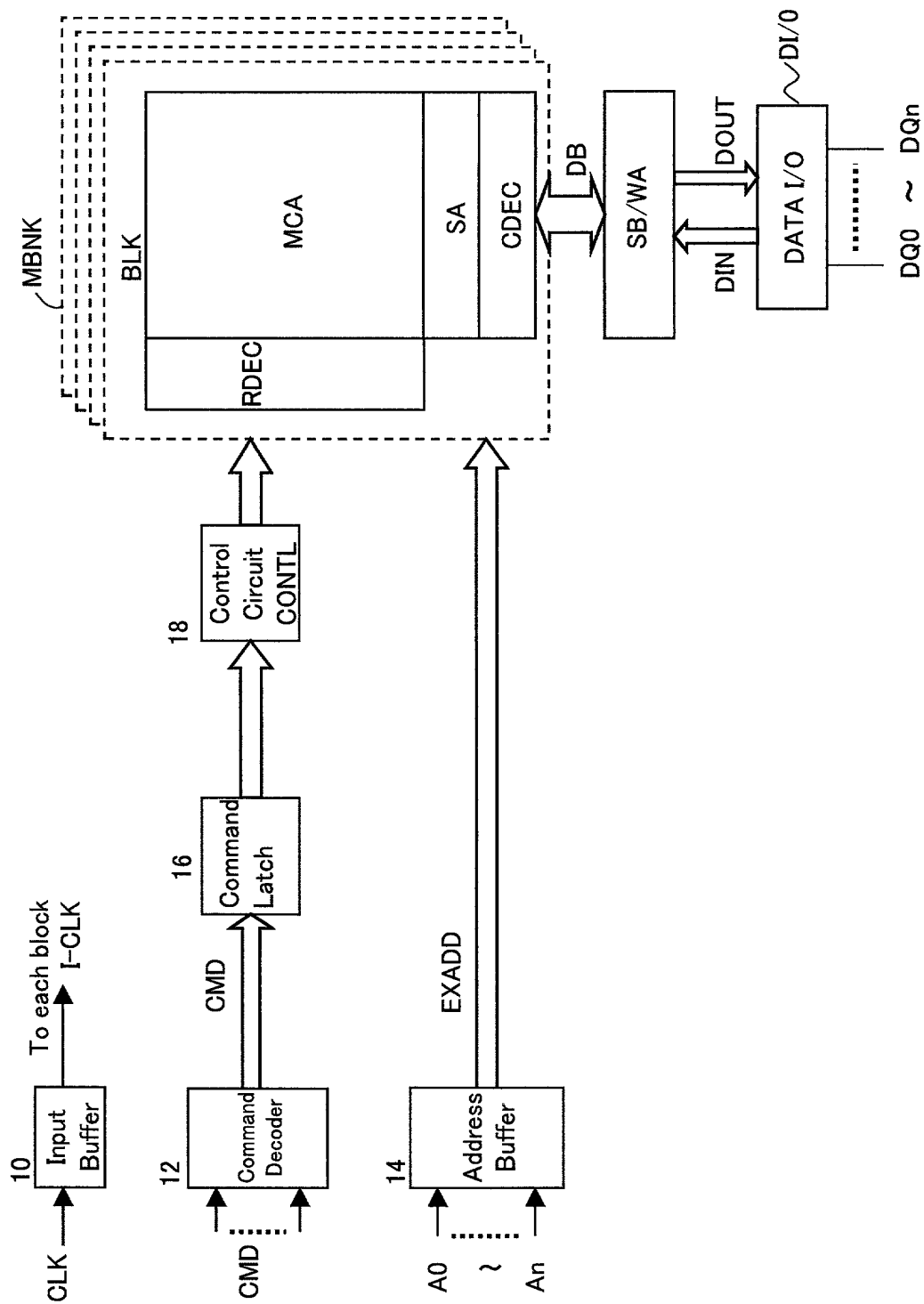


FIG. 3

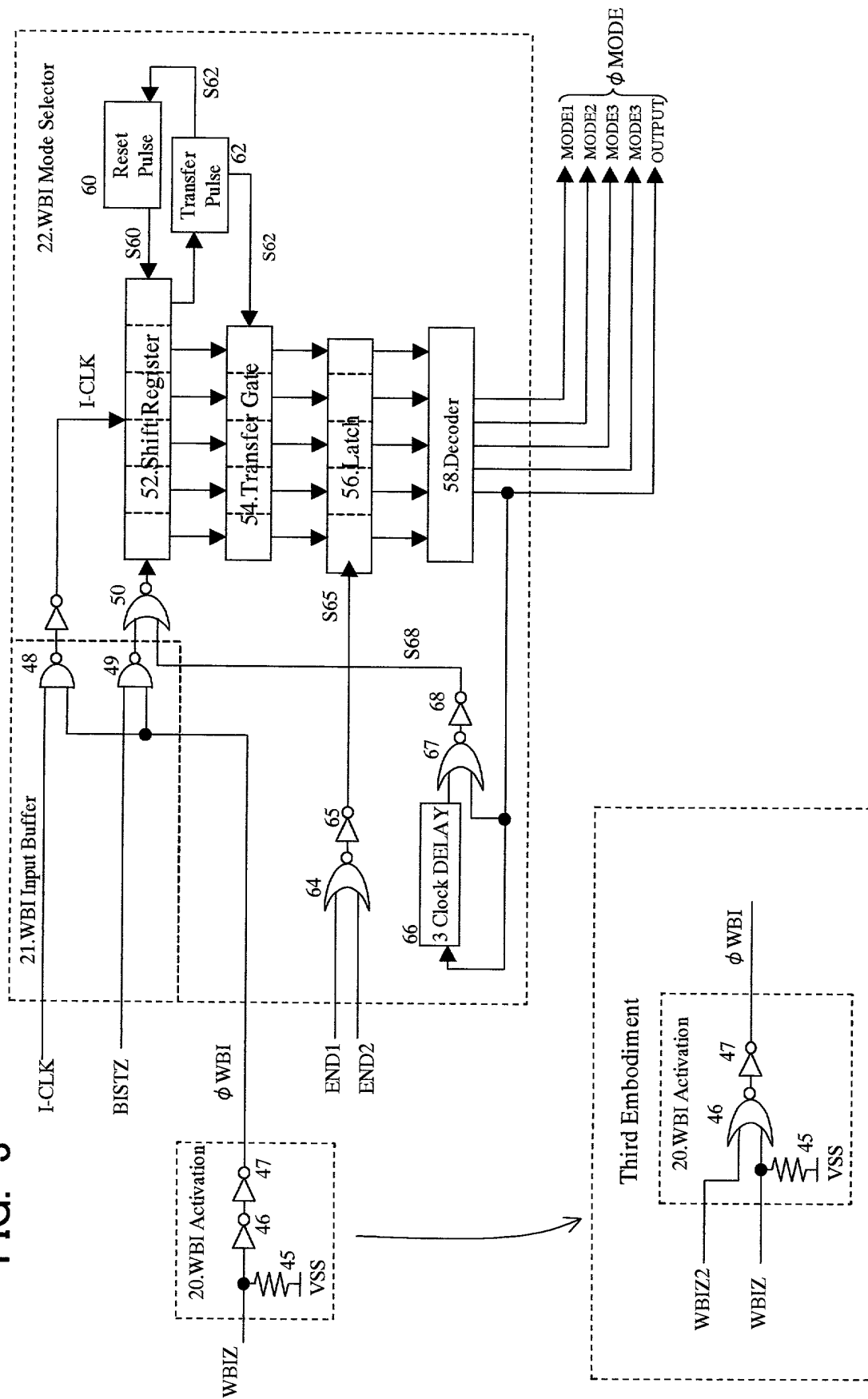


FIG. 4

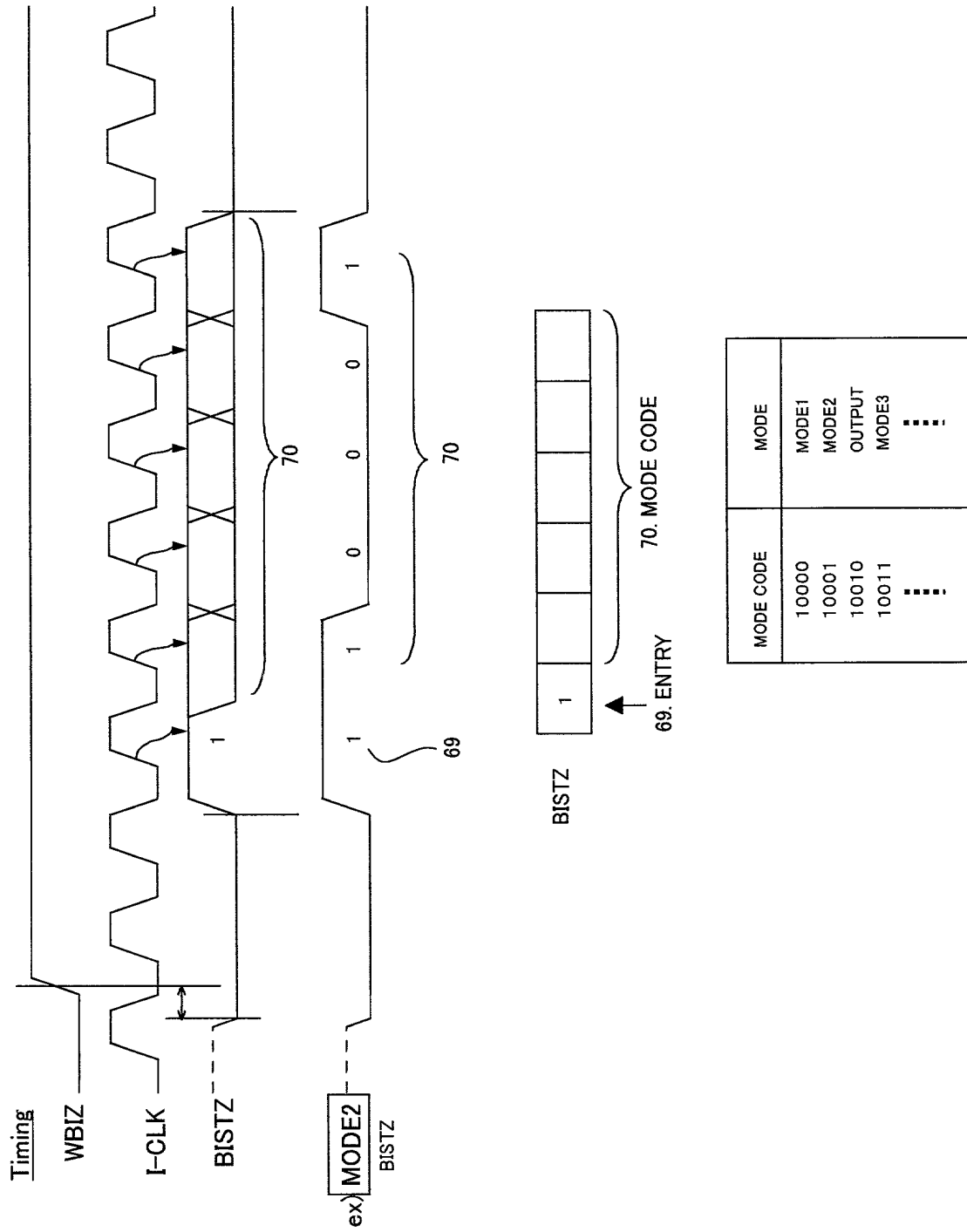


FIG. 5

Timing

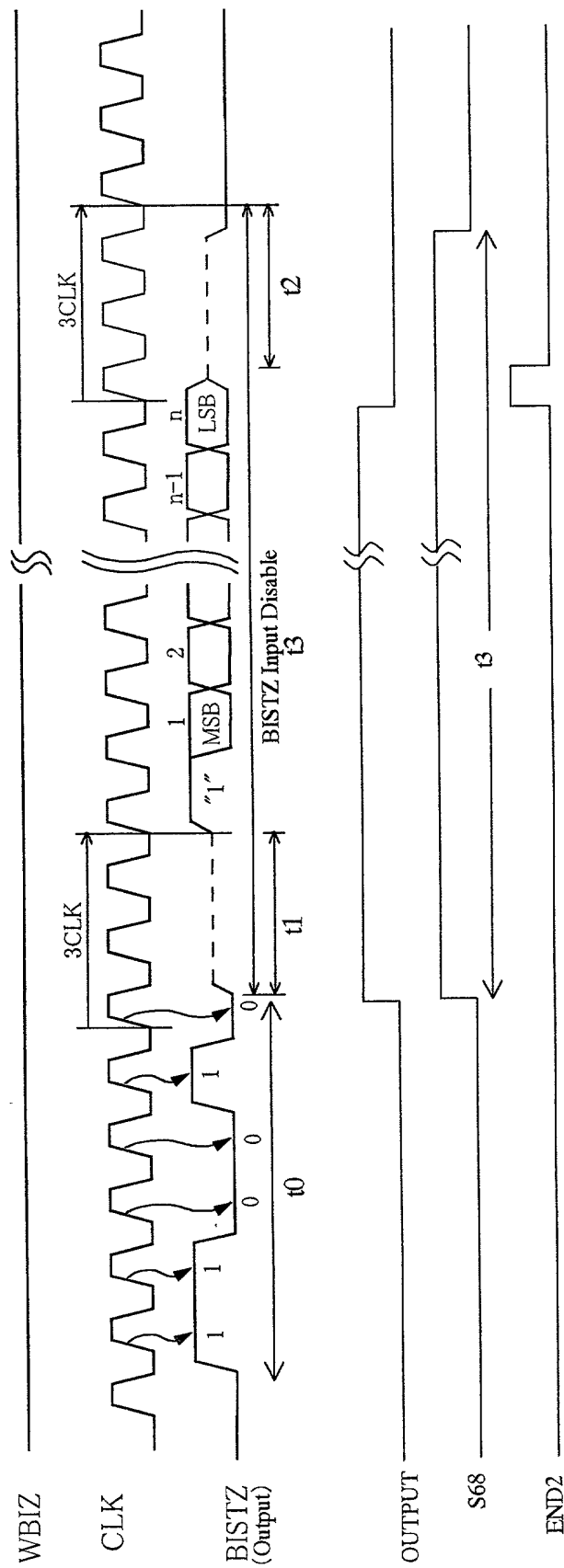


FIG. 7

MODE 1

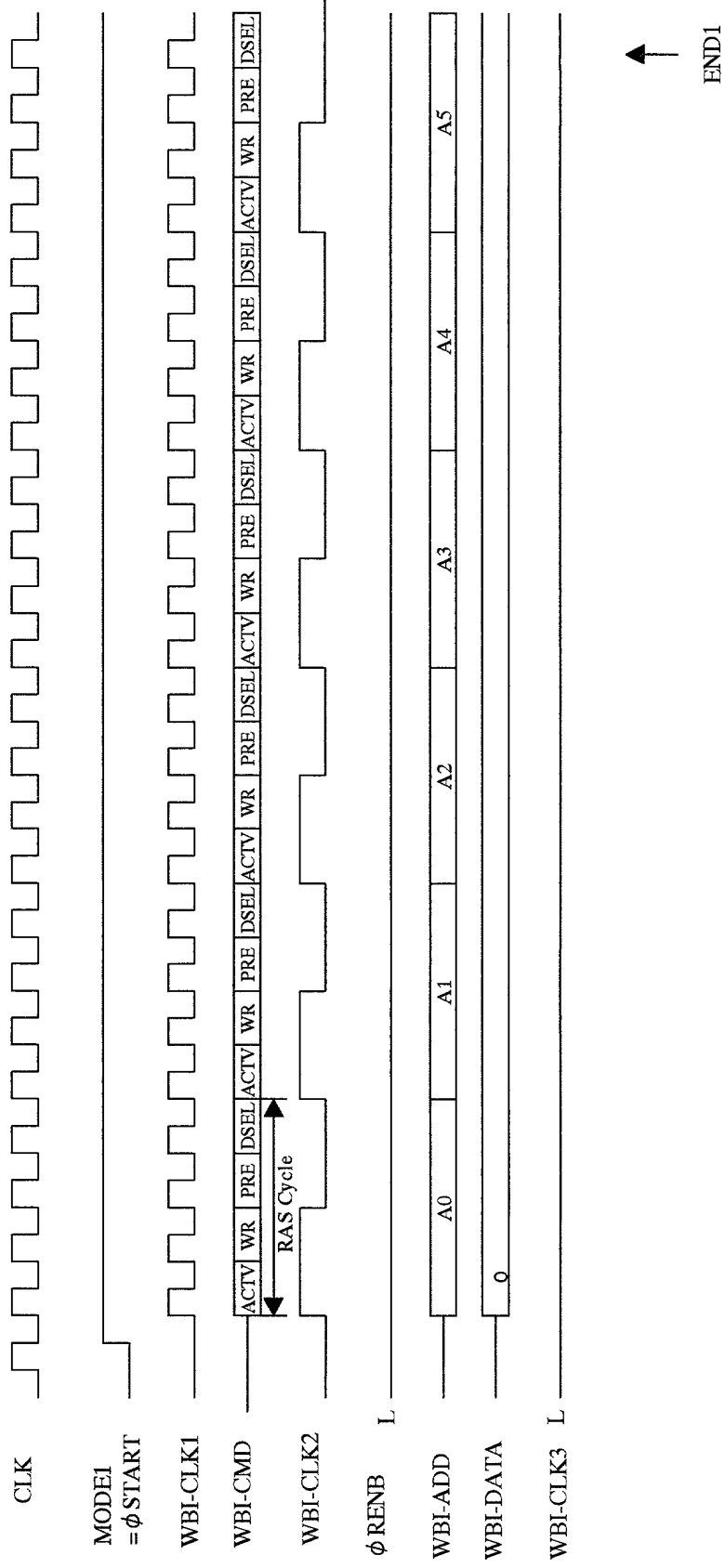
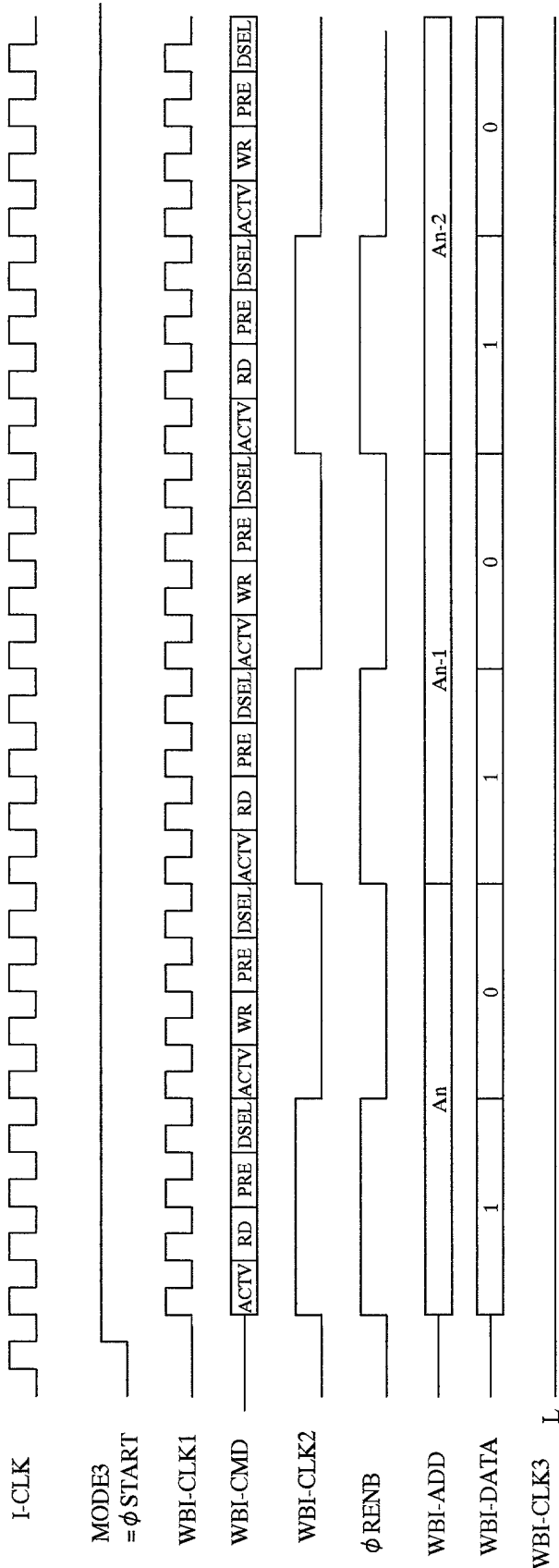


FIG. 9

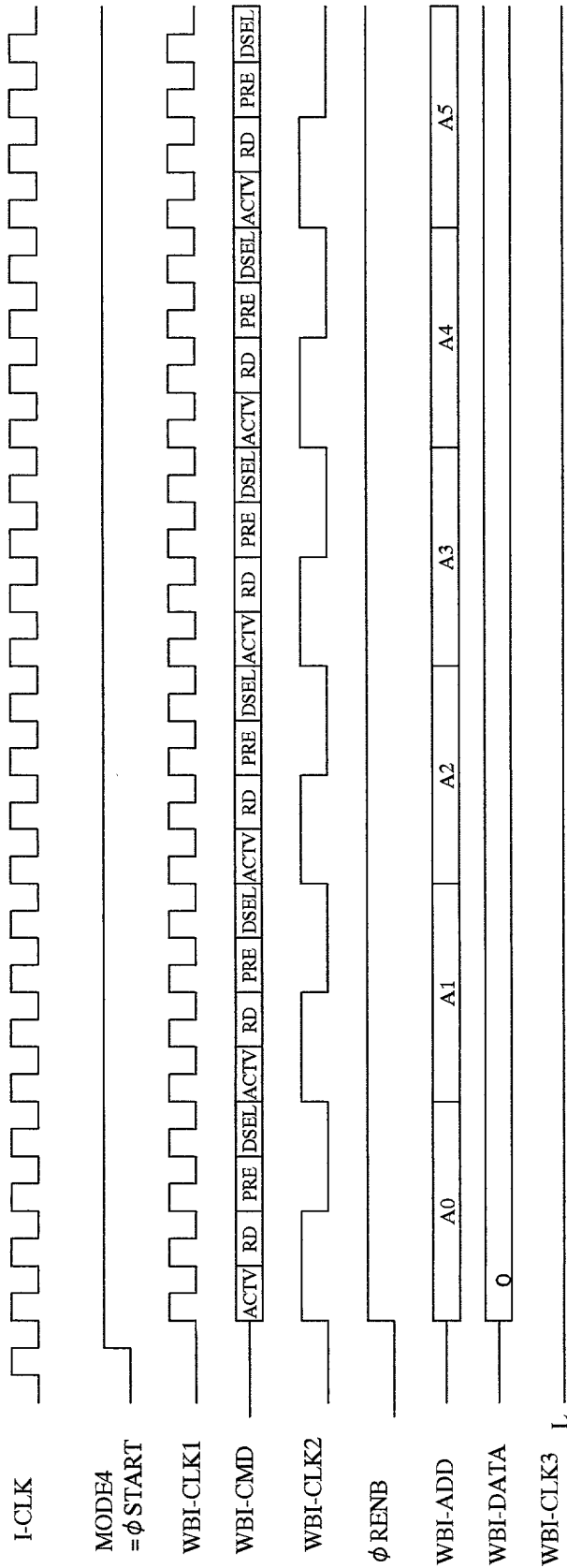
MODE3



↑
END1

FIG. 10

MODE4



↑
END1

FIG. 11

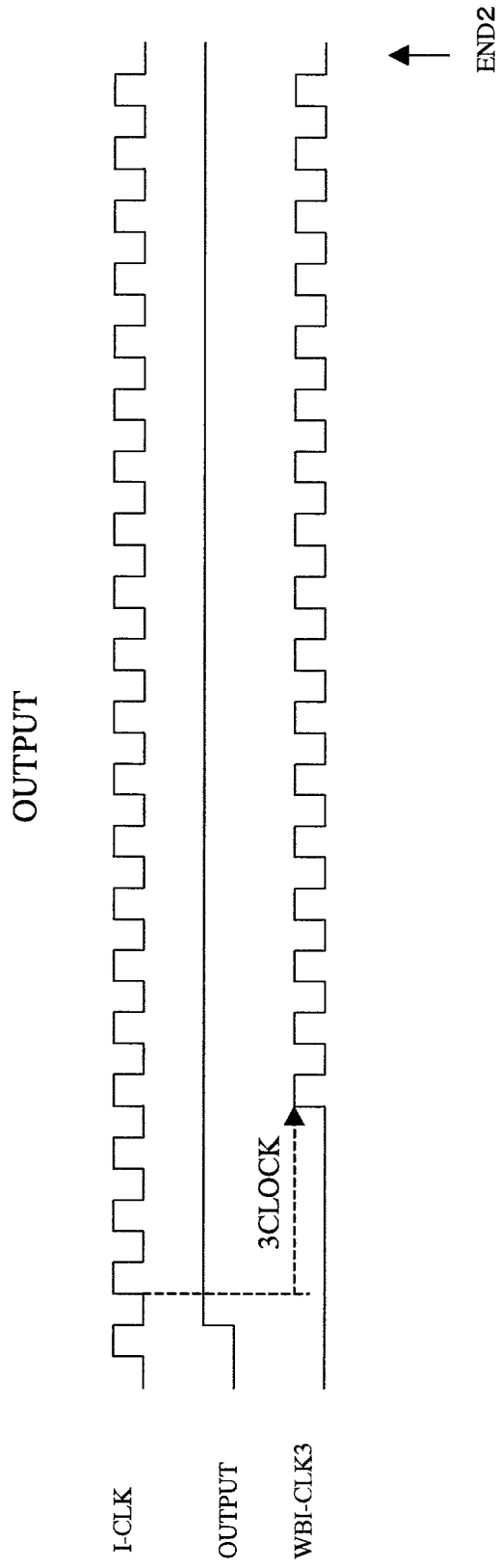


FIG. 12

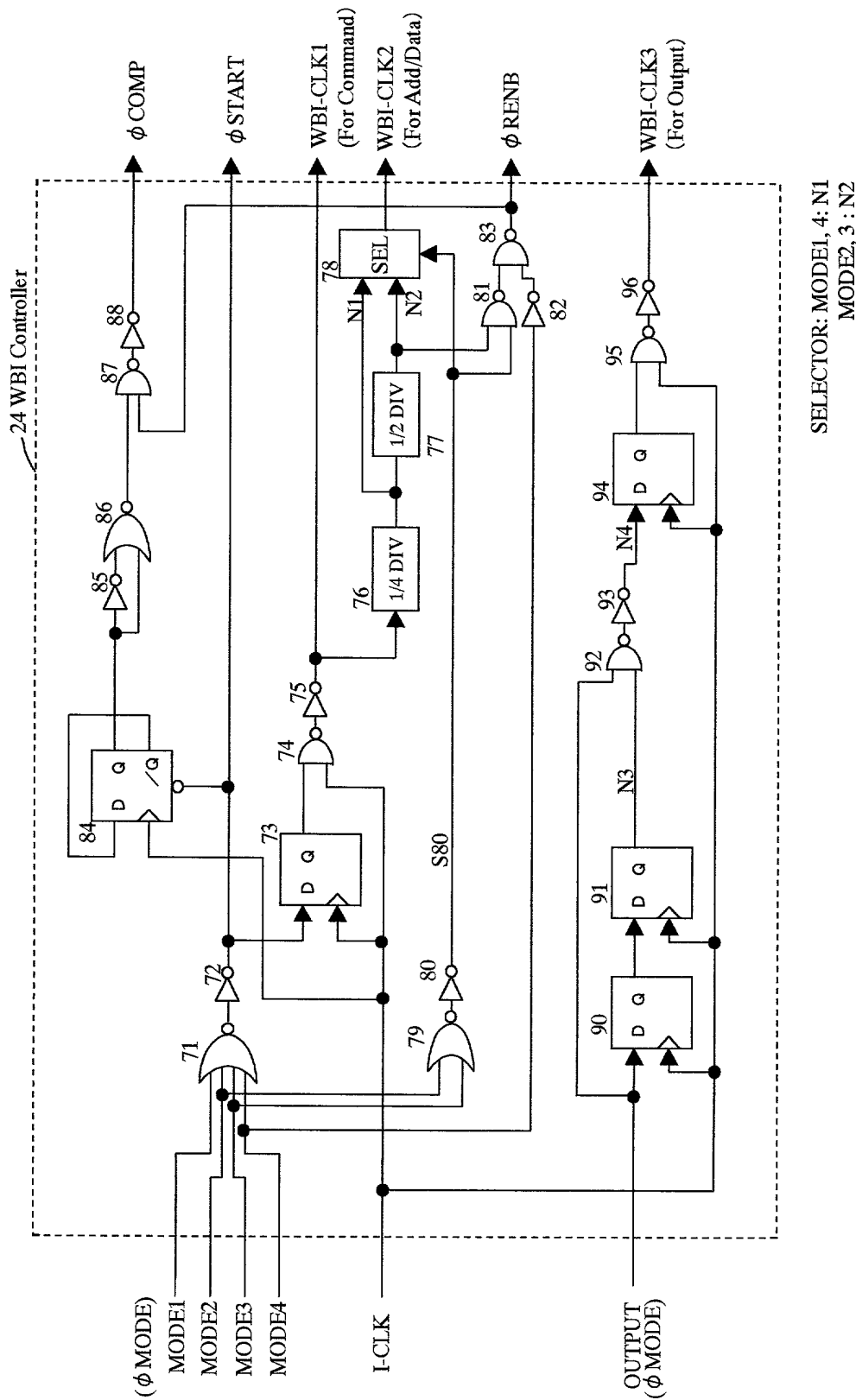


FIG. 13

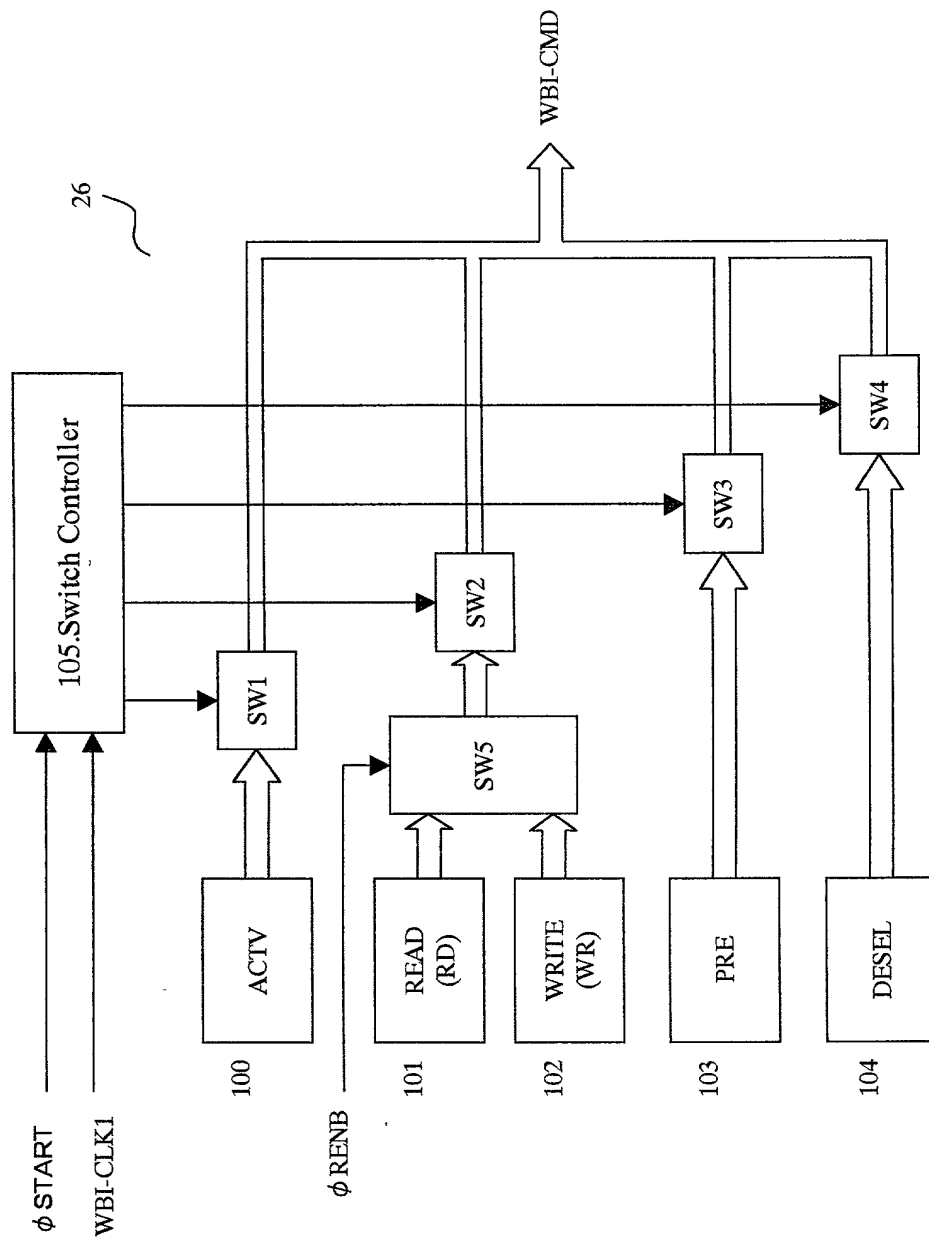


FIG. 15A

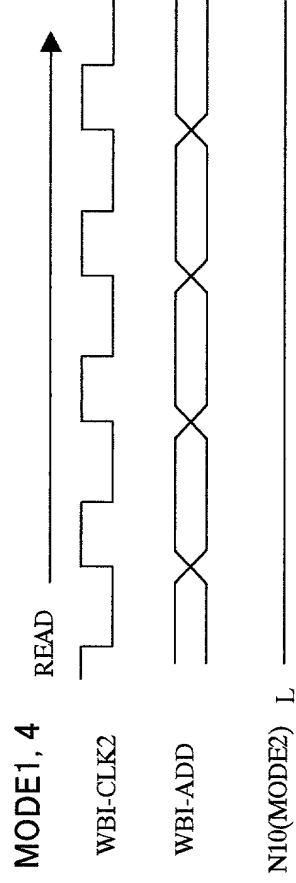


FIG. 15B

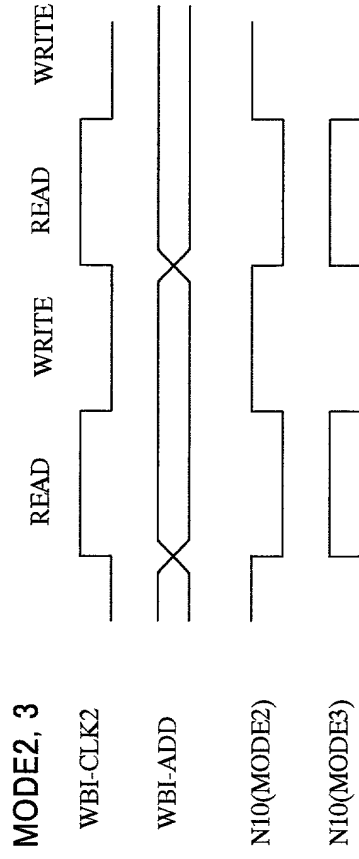


FIG. 15C

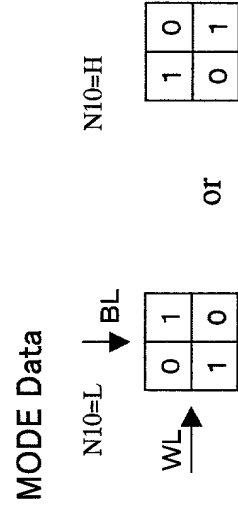


FIG. 16

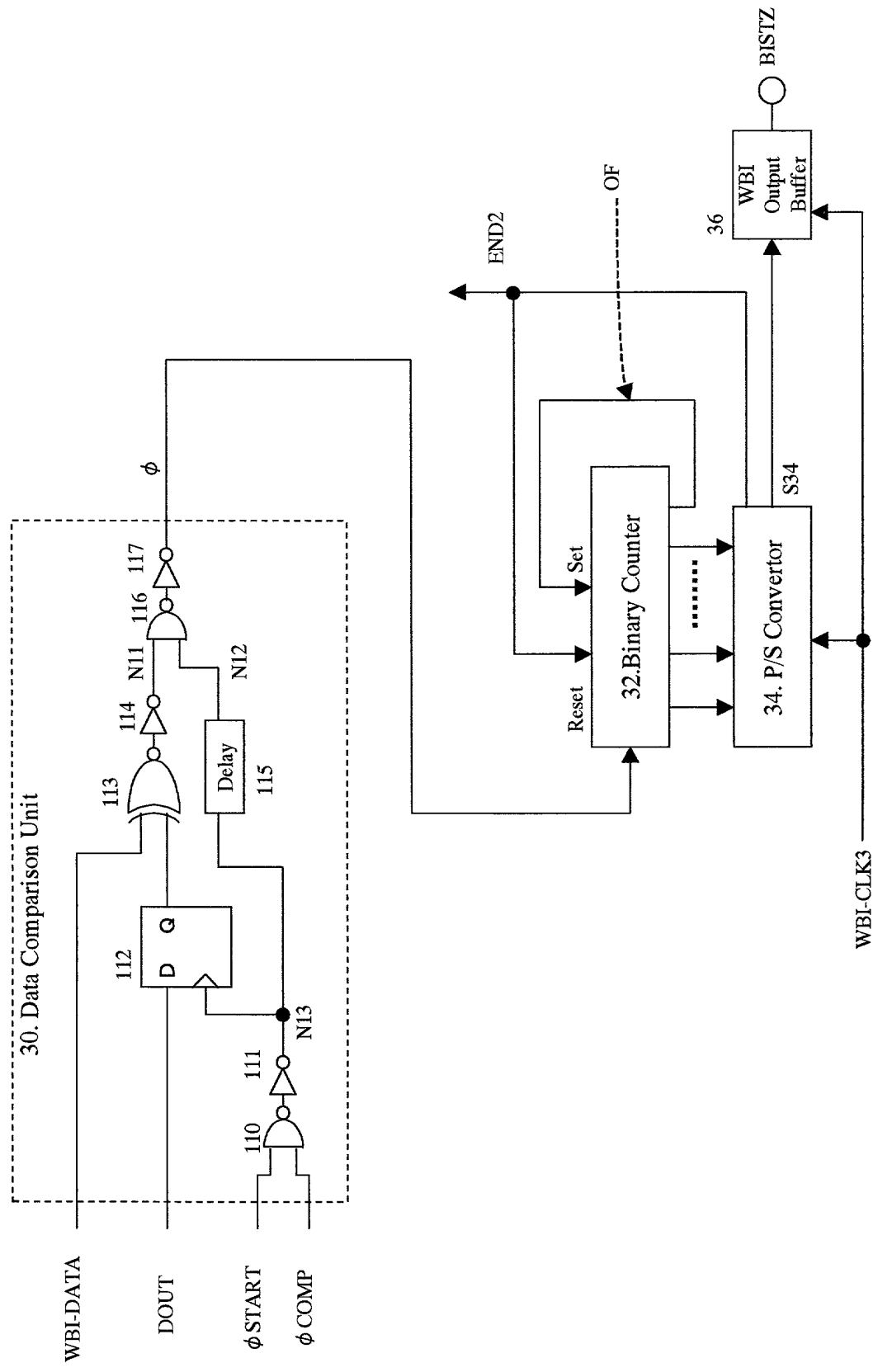


FIG. 17

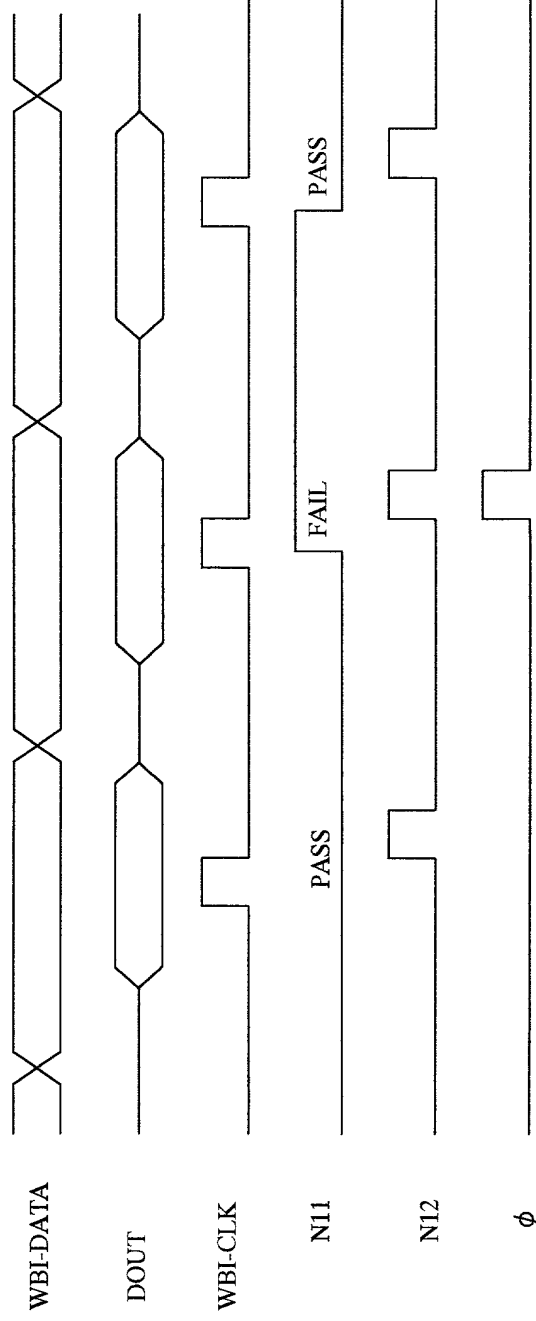


FIG. 18

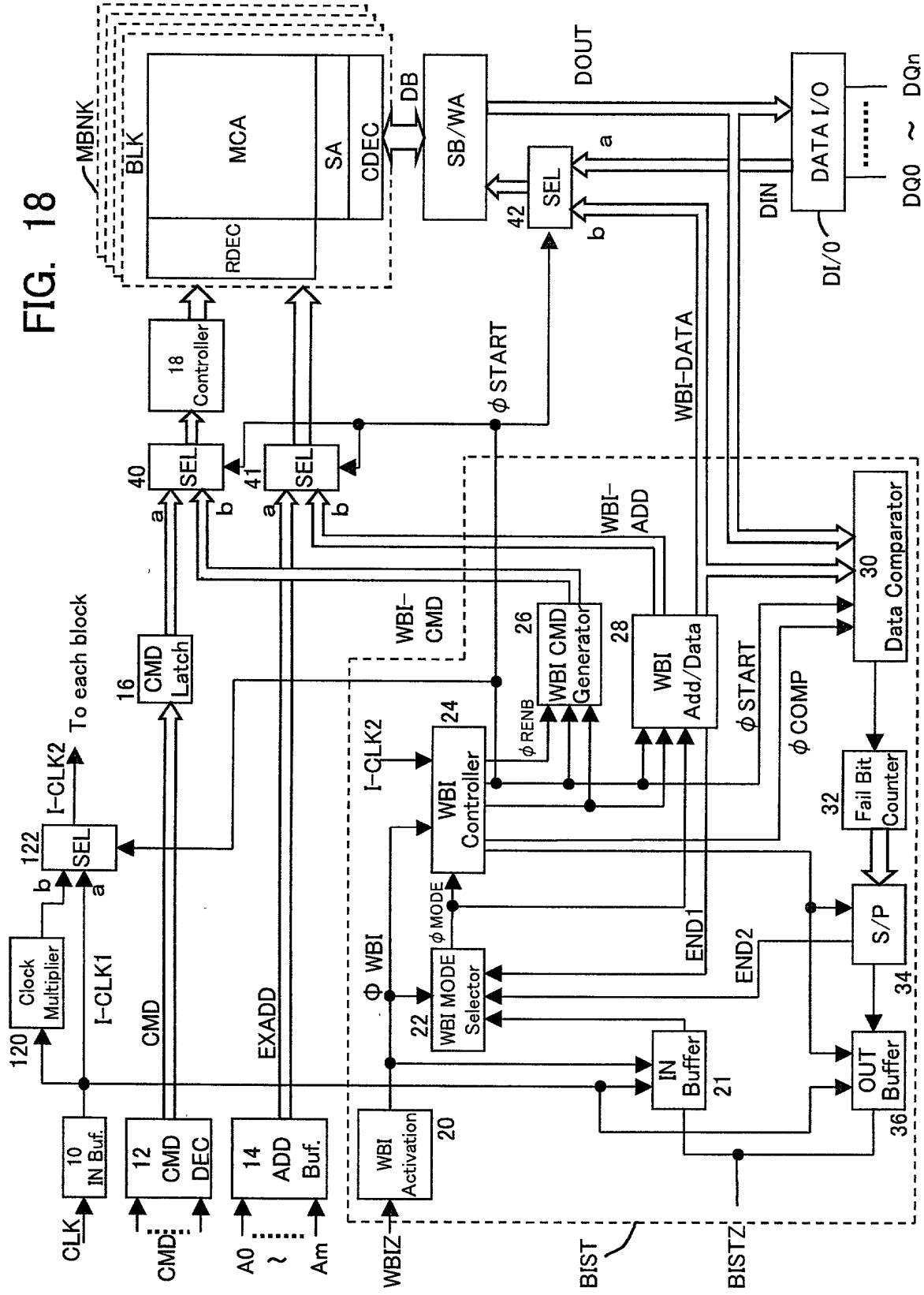
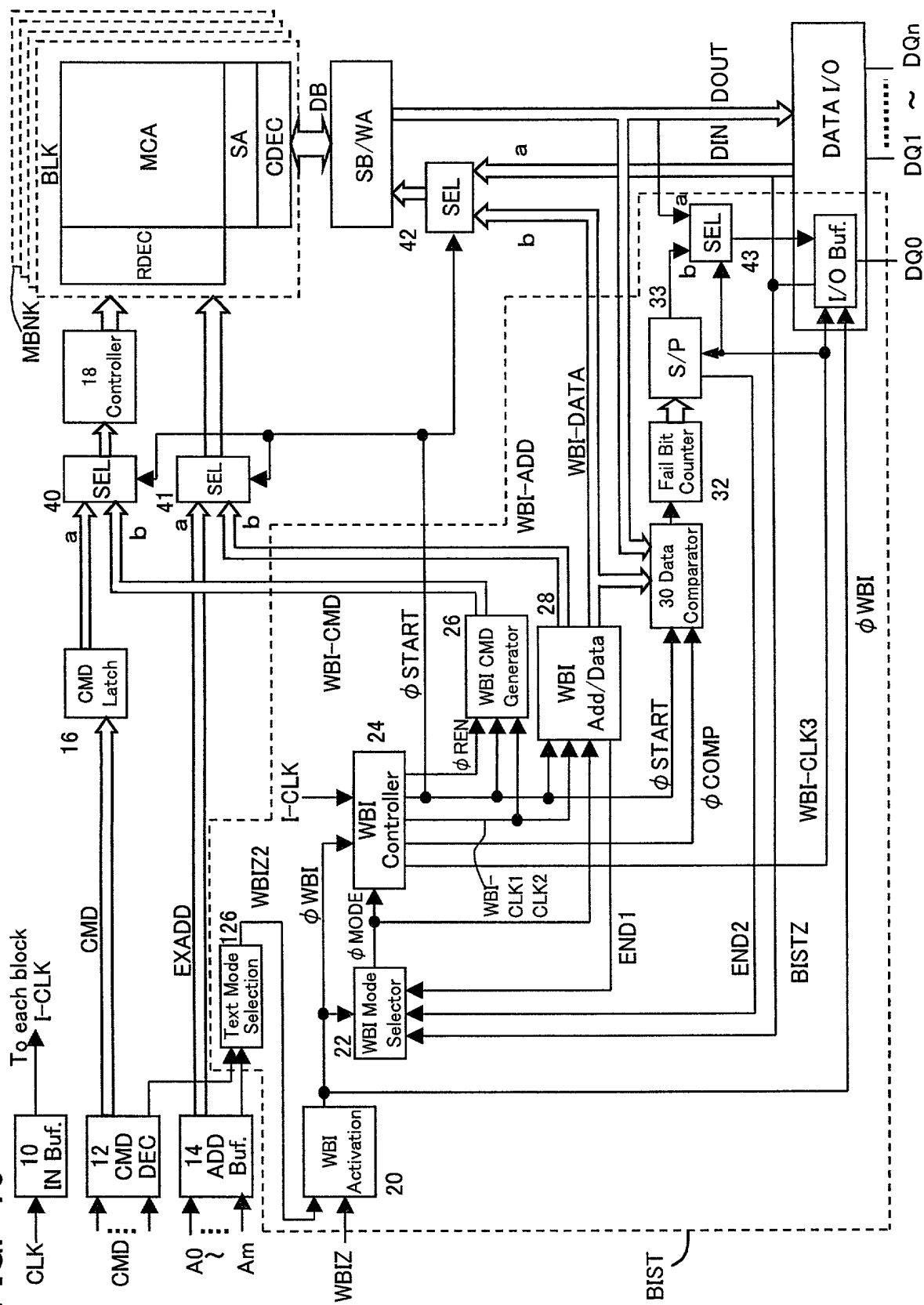
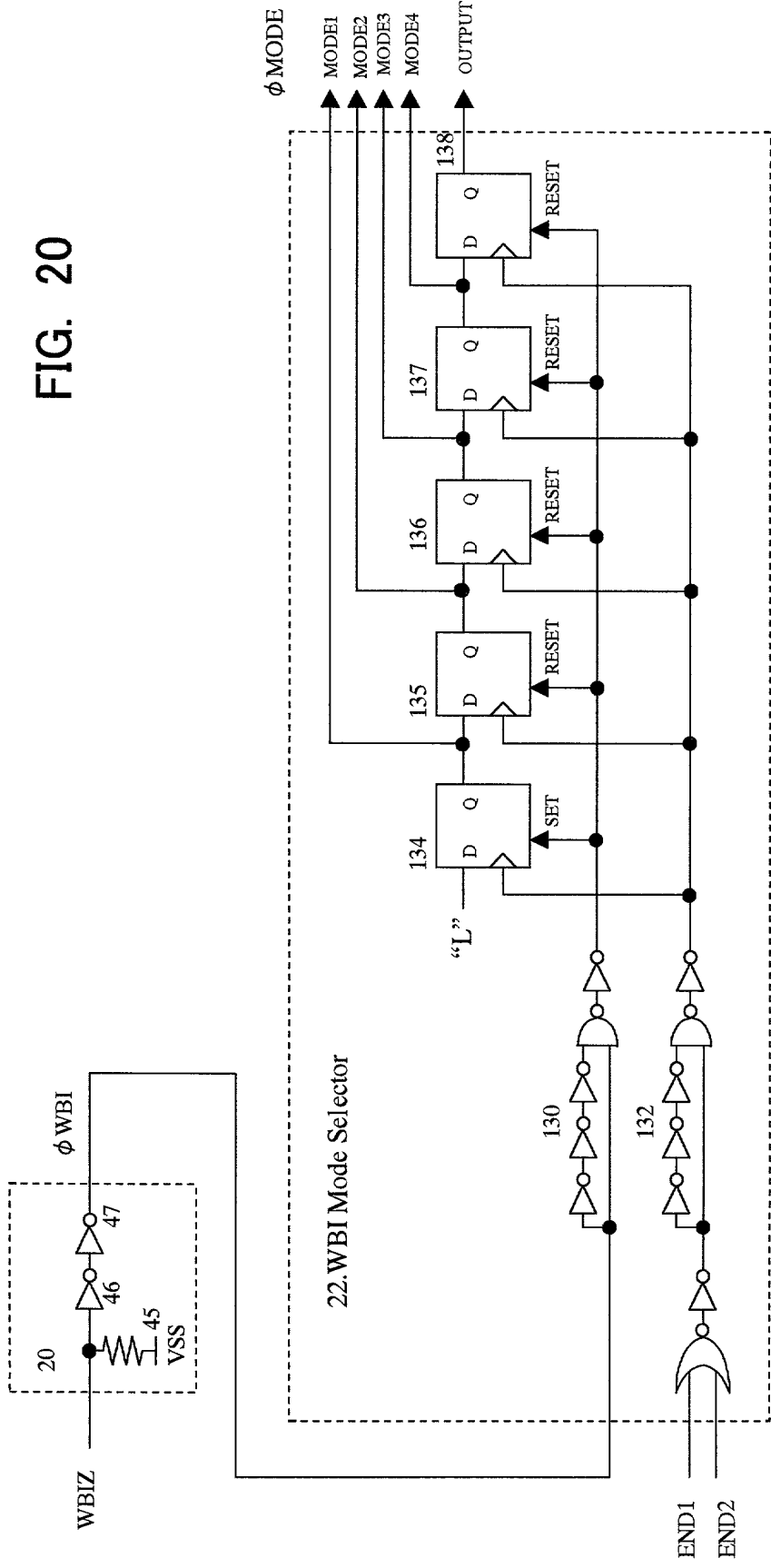


FIG. 19





Q="H": SET

Q="L": RESET

FIG. 21A

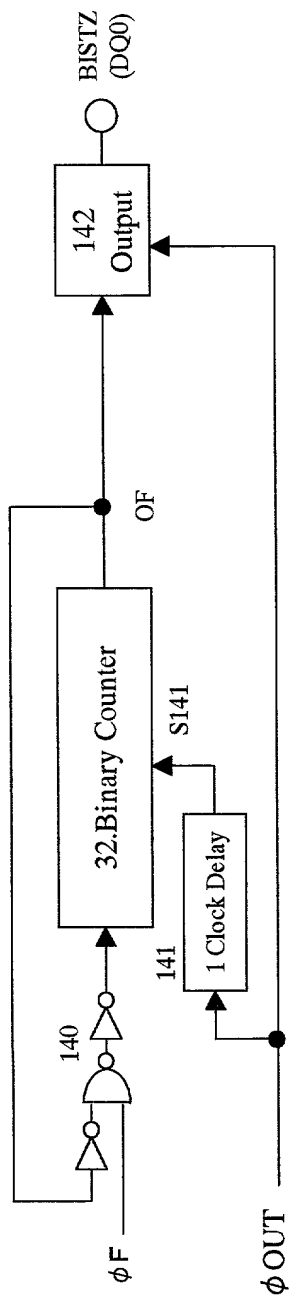


FIG. 21B

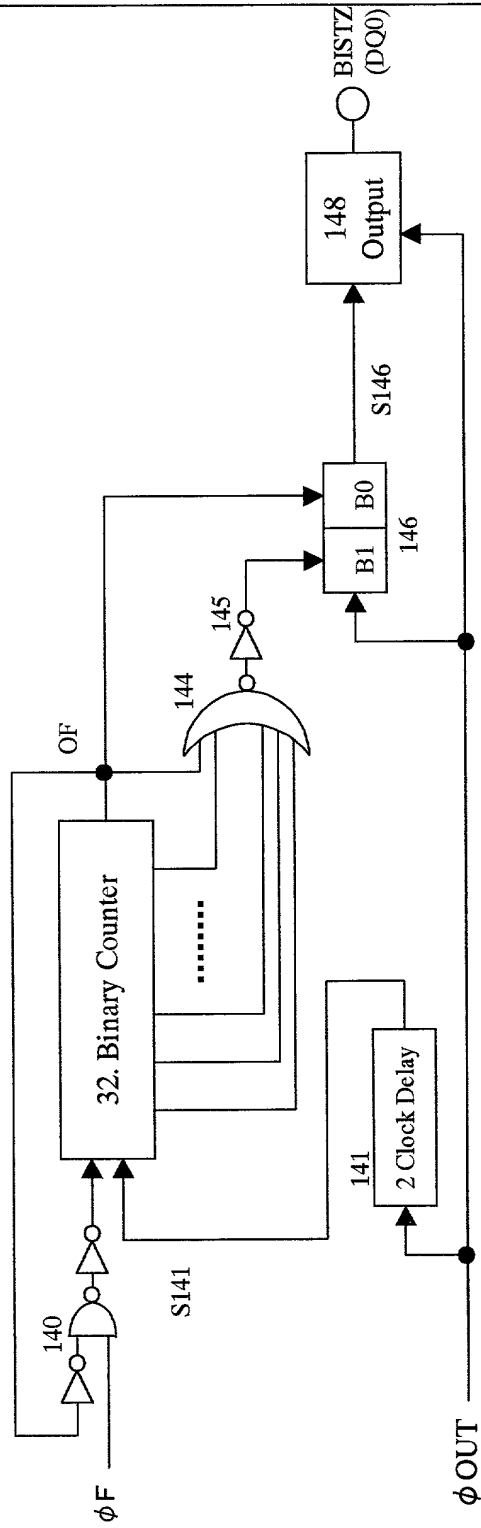


FIG. 22

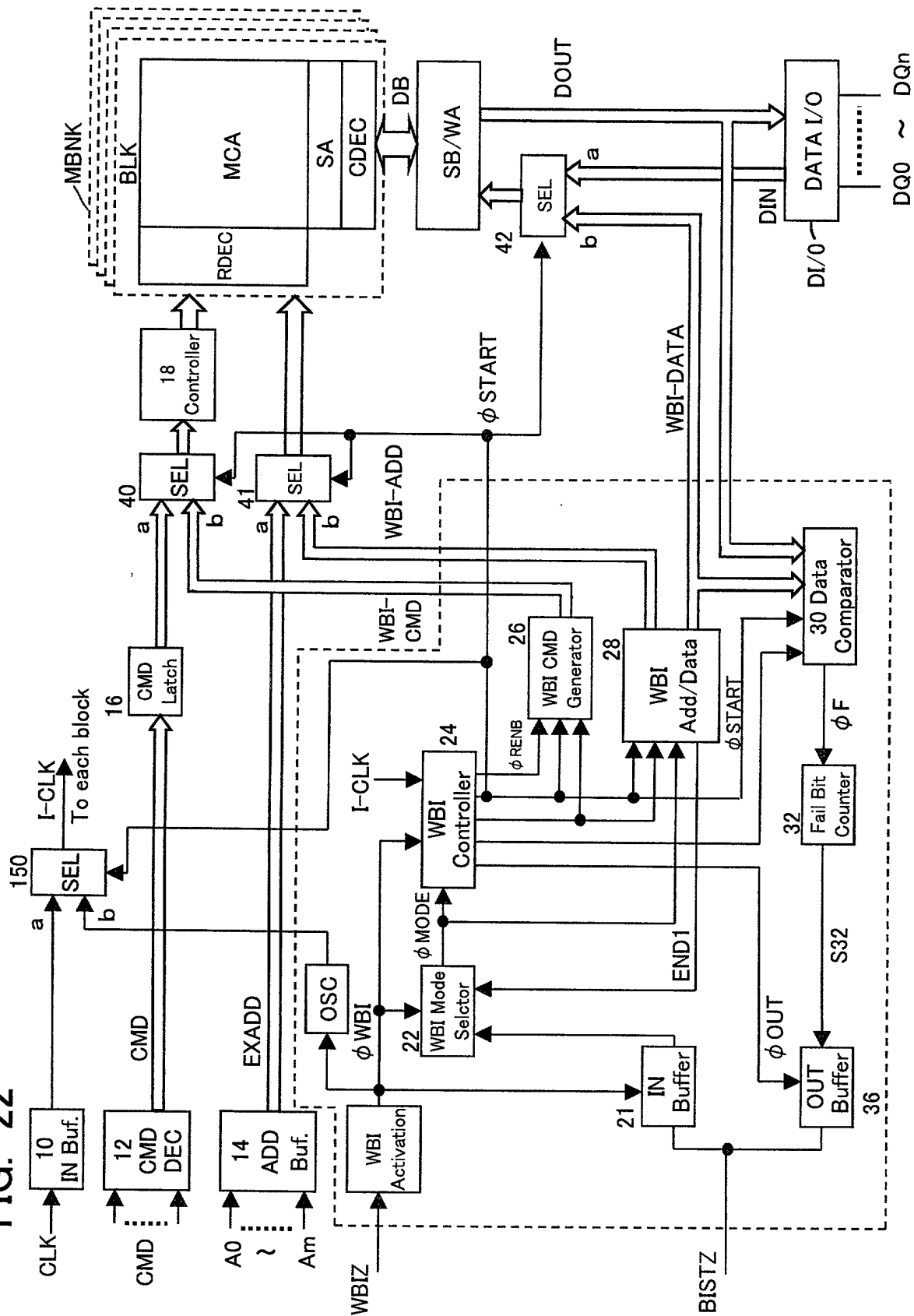
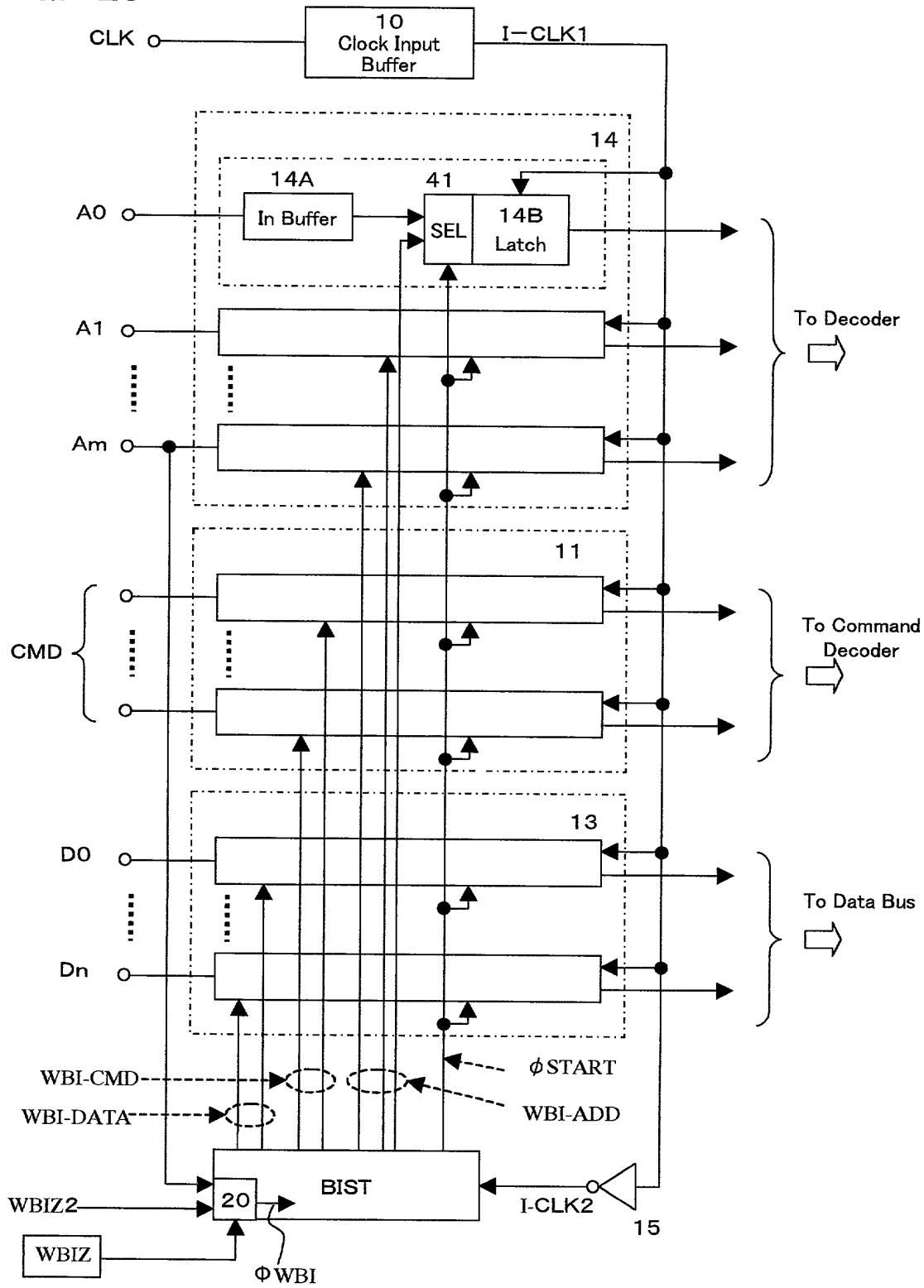


FIG. 23



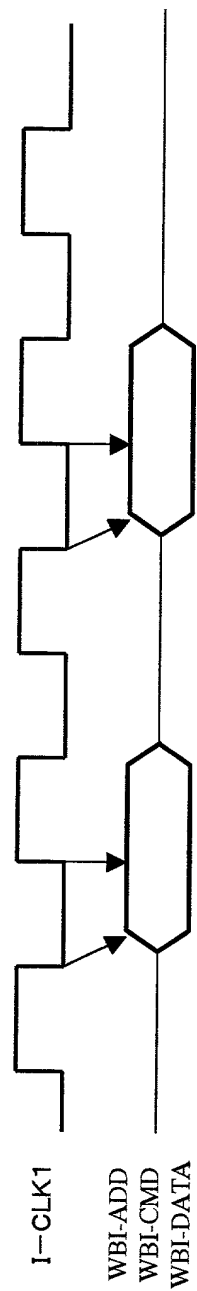


FIG. 24

FIG. 25

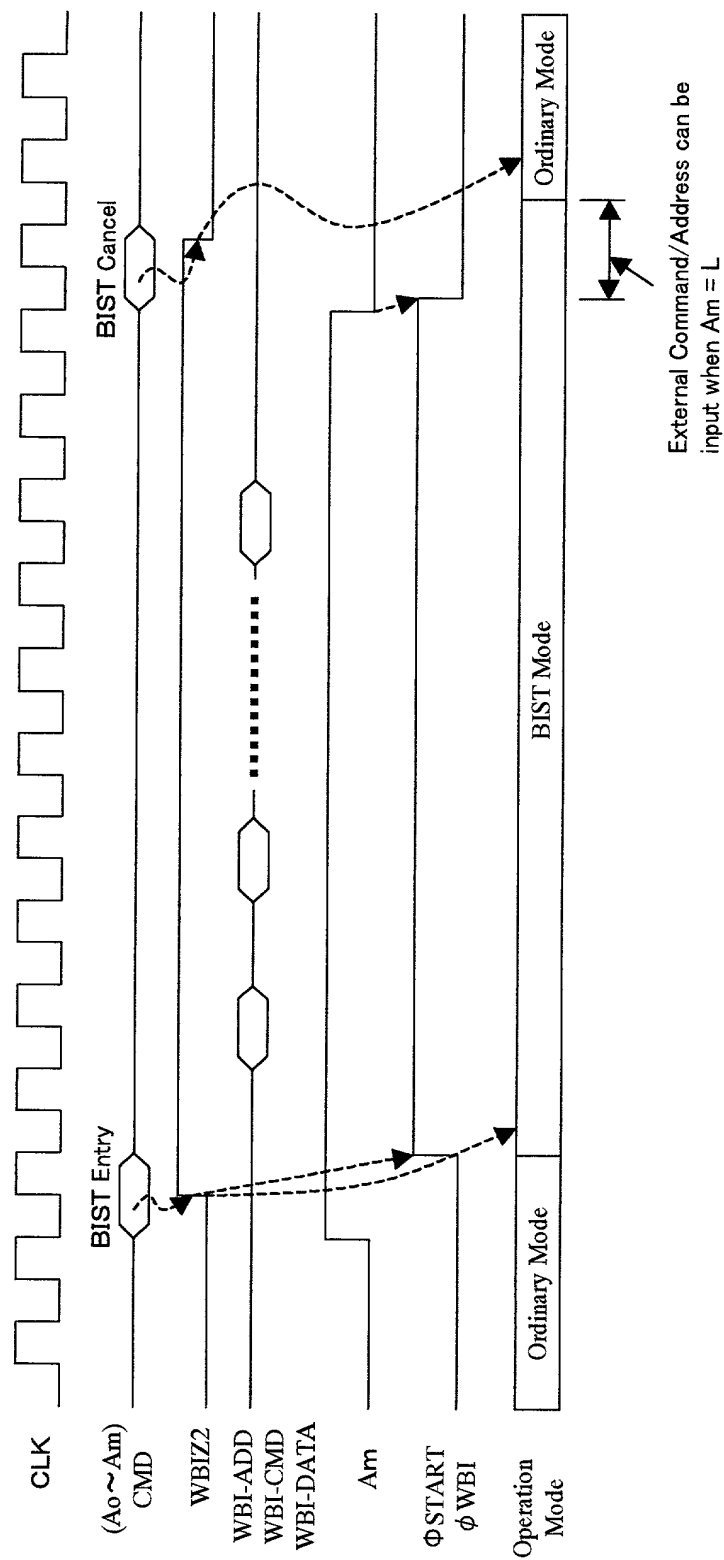


FIG. 26

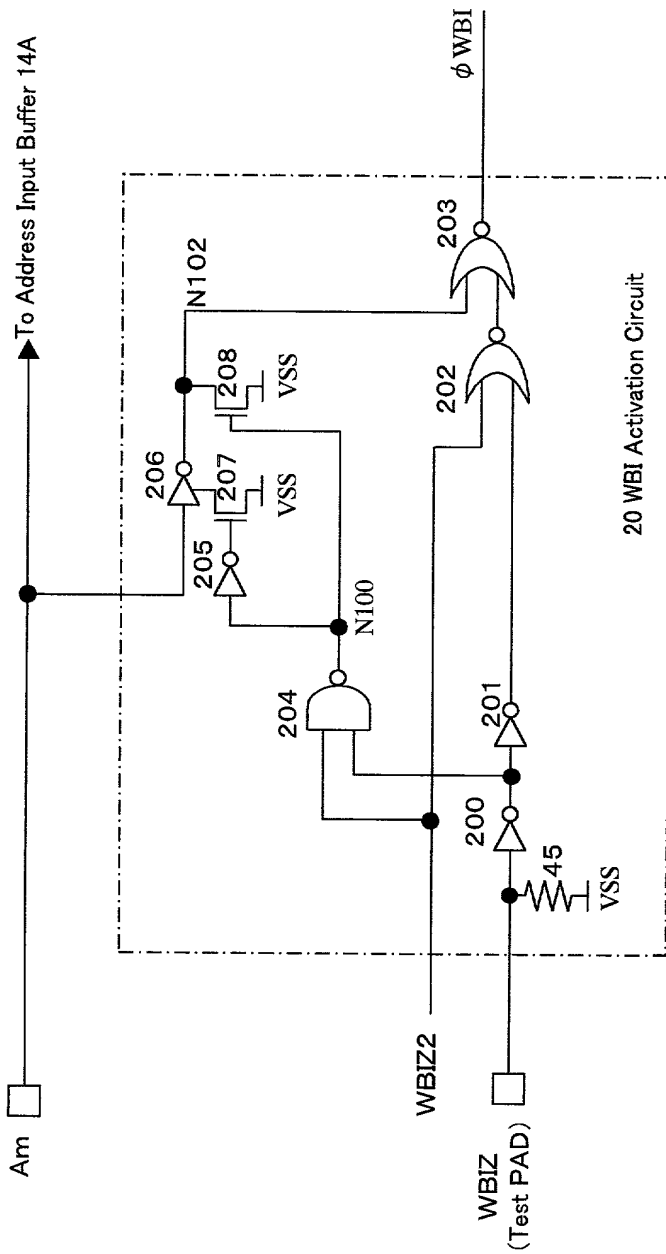


FIG. 27

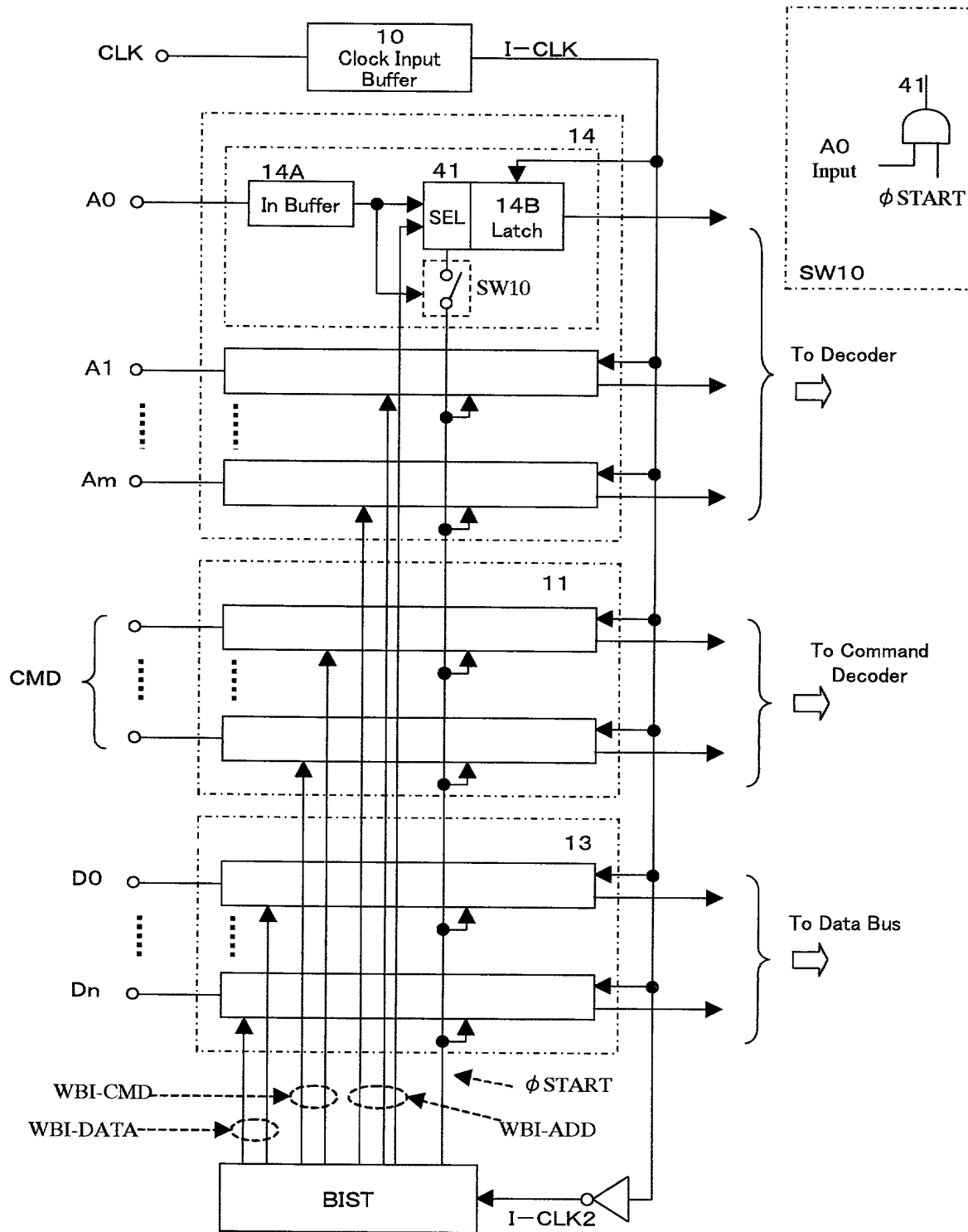
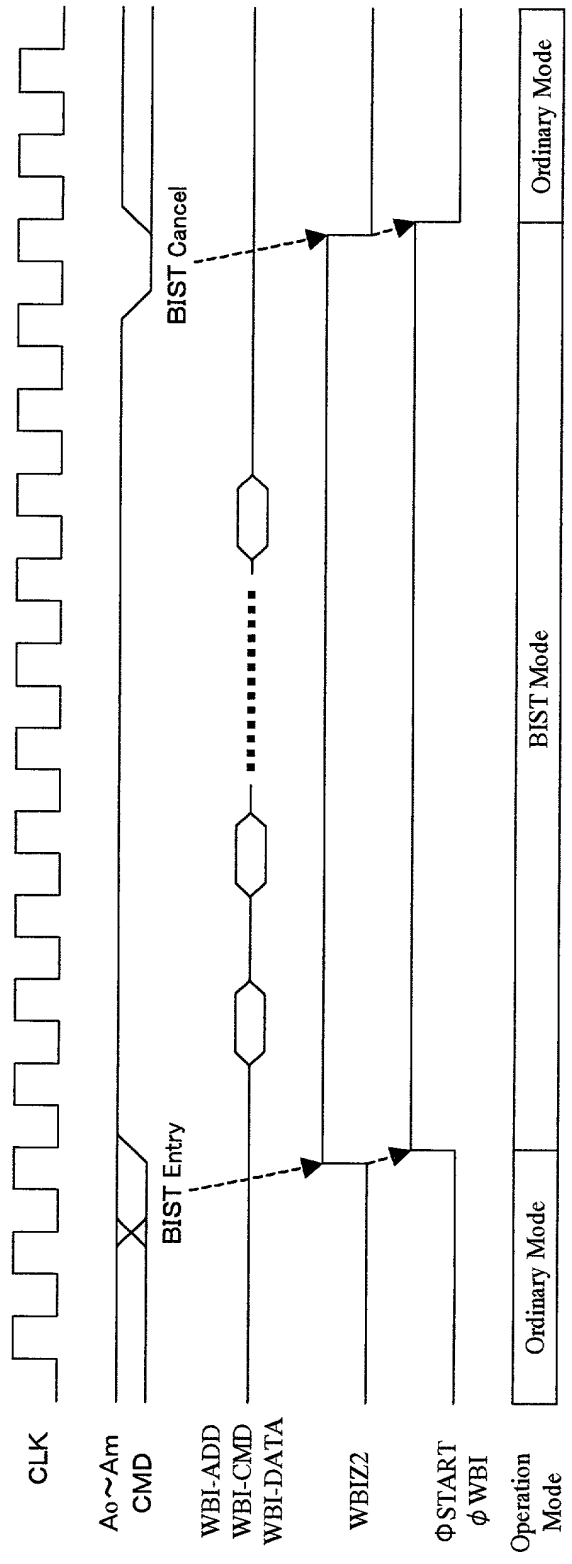


FIG. 28



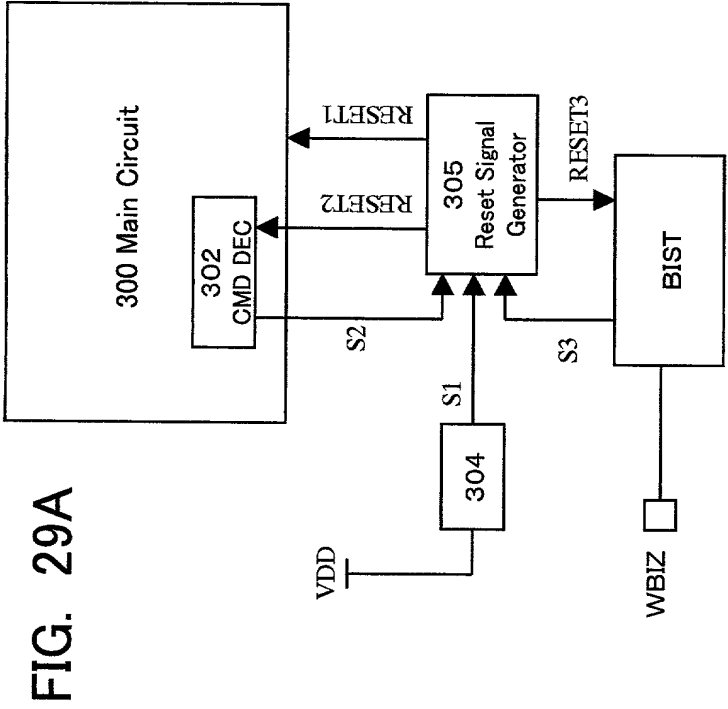
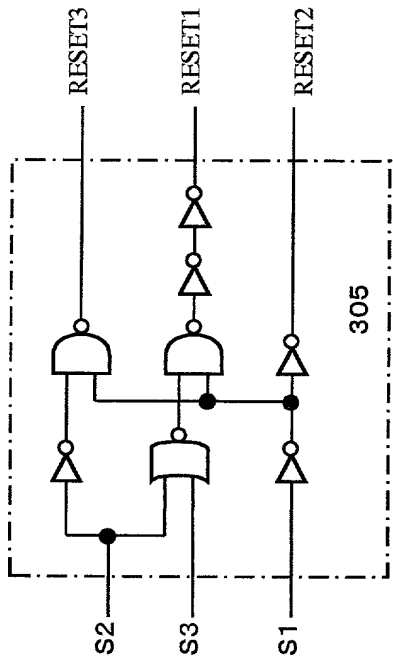


FIG. 29C

	RESET1 (Main)	RESET2 (CMD DEC)	RESET3 (BIST)
S1	○	○	○
S2	○	X	○
S3	○	○	X

○ Reset Signal Generation



Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

Declaration and Power of Attorney For Patent Application

特許出願宣言書及び委任状

Japanese Language Declaration

日本語宣言書

下記の氏名の発明者として、私は以下の通り宣言します。

As a below named inventor, I hereby declare that:

私の住所、私書箱、国籍は下記の私の氏名の後に記載された通りです。

My residence, post office address and citizenship are as stated next to my name.

下記の名称の発明に関して請求範囲に記載され、特許出願している発明内容について、私が最初かつ唯一の発明者（下記の氏名が一つの場合）もしくは最初かつ共同発明者であると（下記の名称が複数の場合）信じています。

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled

SELF-TEST CIRCUIT AND MEMORY DEVICEINCORPORATING IT

上記発明の明細書（下記の欄でx印がついていない場合は、本表に添付）は、

the specification of which is attached hereto unless the following box is checked:

☐ 月 日に提出され、米国出願番号または特許協定条約国際出願番号を _____ とし、
(該当する場合) _____ に訂正されました。☐ was filed on _____
as United States Application Number or
PCT International Application Number
_____ and was amended on
_____ (if applicable).

私は、特許請求範囲を含む上記訂正後の明細書を検討し、内容を理解していることをここに表明します。

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

私は、連邦規則法典第37編第1条56項に定義されるとおり、特許資格の有無について重要な情報を開示する義務があることを認めます。

I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, Section 1.56.

Japanese Language Declaration (日本語宣言書)

私は、米国法典第35編119条(a)-(d)項又は365条(b)項に基づき下記の、米国以外の国の少なくとも一ヶ国を指定している特許出願条約365(a)項に基づく国際出願、又は外国での特許出願もしくは発明者証の出願についての外国優先権をここに主張するとともに、優先権を主張している、本出願の前に出願された特許または発明者証の外国出願を以下に、枠内をマークすることで、示しています。

Prior Foreign Application(s)

外国での先行出願

11-359999

(Number)

(番号)

2000-169689

(Number)

(番号)

Japan

(Country)

(国名)

Japan

(Country)

(国名)

I hereby claim foreign priority under Title 35, United States Code, Section 119 (a)-(d) or 365(b) of any foreign application(s) for patent or inventor's certificate, or 365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below, by checking the box, any foreign application for patent or inventor's certificate, or PCT International application having a filing date before that of the application on which priority is claimed.

Priority Not Claimed

優先権主張なし

17/12/1999

(Day/Month/Year Filed)

(出願年月日)

06/06/2000

(Day/Month/Year Filed)

(出願年月日)

私は、第35編米国法典119条(e)項に基づいて下記の米国特許出願規定に記載された権利をここに主張いたします。

(Application No.)

(出願番号)

(Filing Date)

(出願日)

私は、下記の米国法典第35編120条に基づいて下記の米国特許出願に記載された権利、又は米国を指定している特許協力条約365条(c)に基づき権利をここに主張します。また、本出願の各請求範囲の内容が米国法典第35編112条第1項又は特許協力条約で規定された方法で先行する米国特許出願に開示されていない限り、その先行米国出願書提出日以降で本出願書の日本国内または特許協力条約国際提出日までの期間中に入手された、連邦規則法典第37編1条56項で定義された特許資格の有無に関する重要な情報について開示義務があることを認識しています。

(Application No.)

(出願番号)

(Filing Date)

(出願日)

(Application No.)

(出願番号)

(Filing Date)

(出願日)

私は、私自身の知識に基づいて本宣言書中で私が行なう表明が真実であり、かつ私の入手した情報と私の信じていることに基づき表明が全て真実であると信じていること、さらに故意になされた虚偽の表明及びそれと同等の行為は米国法典第18編第1001条に基づき、罰金または拘禁、もしくはその両方により処罰されること、そしてそのような故意による虚偽の声明を行なえば、出願した、又は既に許可された特許の有効性が失われることを認識し、よってここに上記のごとく宣言を致します。

I hereby claim the benefit under Title 35, United States Code, Section 119(e) of any United States provisional application(s) listed below.

(Application No.)

(出願番号)

(Filing Date)

(出願日)

I hereby claim the benefit under Title 35, United States Code, Section 120 of any United States application(s), or 365(c) of any PCT International application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT International application in the manner provided by the first paragraph of Title 35, United States Code Section 112, I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, Section 1.56 which became available between the filing date of the prior application and the national or PCT International filing date of application.

(Status: Patented, Pending, Abandoned)

(現況: 特許許可済、係属中、放棄済)

(Status: Patented, Pending, Abandoned)

(現況: 特許許可済、係属中、放棄済)

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Japanese Language Declaration (日本語宣言書)

委任状: 私は下記の発明者として、本出願に関する一切の手続きを特許庁長官に対して遂行する代理または代理人として、下記の者を指名いたします。(弁護士、または代理人の氏名及び登録番号を明記のこと)

POWER OF ATTORNEY: As a named inventor, I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and transact all business in the Patent and Trademark Office connected therewith (list name and registration number)

書頭送付先

And I hereby appoint as principal attorneys: David T. Nikaido, Reg. No. 22,663; Charles M. Marmelstein, Reg. No. 25,895; George E. Oram, Jr., Reg. No. 27,931; Robert B. Murray, Reg. No. 22,980; E. Marcie Emas, Reg. No. 32,131; Douglas H. Goldhush, Reg. No. 33,125; Monica Chin Kitts, Reg. No. 36,105; Richard J. Berman, Reg. No. 39,107; King L. Wong, Reg. No. 37,500; Karen K. Costantino, Reg. No. 35,107; James A. Poulos, III, Reg. No. 31,714; Patrick D. Muir, Reg. No. 37,403; Sharon N. Kiesner, Reg. No. 36,335; and Murat Ozgu, Reg. No. 44,275; Bradley D. Goldizen, Reg. No. 43,637; and N. Alexander Nolte, Reg. No. 45,689.

通信電話連絡元: (名前及び電話番号)

Please direct all communications to the following address:
ARENT FOX KINTNER PLOTKIN & KAHN, PLLC
1050 Connecticut Avenue, N.W., Suite 600
Washington, D.C. 20036-5339
Tel: (202) 857-6000; Fax: (202) 857-6395

唯一または第一発明者名	Full name of sole or first inventor
	Yukihiro NOMURA
発明者の署名	Inventor's signature
日付	Date
	Yukihiro Nomura 05/09/2000
住所	Residence
	Kawasaki, Japan
国籍	Citizenship
	Japan
私書箱	Post Office Address
	c/o FUJITSU LIMITED, 1-1, Kamikodanaka 4-chome,
	Nakahara-ku, Kawasaki, 211-8588 Japan
第二共同発明者名	Full name of second joint inventor, if any
	Hiroyuki FUJIMOTO
第二共同発明者の署名	Second inventor's signature
日付	Date
	Hiroyuki Fujimoto 05/09/2000
住所	Residence
	Kawasaki, Japan
国籍	Citizenship
	Japan
私書箱	Post Office Address
	c/o FUJITSU LIMITED, 1-1, Kamikodanaka 4-chome,
	Nakahara-ku, Kawasaki, 211-8588 Japan

(第三以降の共同発明者についても同様に記載し、署名をすること)

(Supply similar information and signature for third and subsequent joint inventors.)

第三共同発明者名		Full name of third joint inventor, if any Takahiro SUZUKI	
第三共同発明者の署名	日付	Third inventor's signature Takahiro Suzuki	Date 05/09/2000
住所	Residence Kawasaki, Japan		
国籍	Citizenship Japan		
私書箱	Post Office Address c/o FUJITSU LIMITED, 1-1, Kamikodanaka 4-chome, Nakahara-ku, Kawasaki, 211-8588 Japan		
第四共同発明者名		Full name of fourth joint inventor, if any Tatsuya KANDA	
第四共同発明者の署名	日付	Fourth inventor's signature Tatsuya Kanda	Date 05/09/2000
住所	Residence Kawasaki, Japan		
国籍	Citizenship Japan		
私書箱	Post Office Address c/o FUJITSU LIMITED, 1-1, Kamikodanaka 4-chome, Nakahara-ku, Kawasaki, 211-8588 Japan		
第五共同発明者名		Full name of fifth joint inventor, if any Yasuro MATSUZAKI	
第五共同発明者の署名	日付	Fifth inventor's signature Yasuro Matsuzaki	Date 05/09/2000
住所	Residence Kawasaki, Japan		
国籍	Citizenship Japan		
私書箱	Post Office Address c/o FUJITSU LIMITED, 1-1, Kamikodanaka 4-chome, Nakahara-ku, Kawasaki, 211-8588 Japan		
第六共同発明者名		Full name of sixth joint inventor, if any Masahiko SATTOU	
第六共同発明者の署名	日付	Sixth inventor's signature Masahiko Saitou	Date 05/09/2000
住所	Residence Kawasaki, Japan		
国籍	Citizenship Japan		
私書箱	Post Office Address c/o FUJITSU LIMITED, 1-1, Kamikodanaka 4-chome, Nakahara-ku, Kawasaki, 211-8588 Japan		

第七共同発明者名		Full name of seventh joint inventor, if any	
		Hiroyoshi TOMITA	
第七共同発明者の署名	日付	Seventh inventor's signature	Date
		Hiroyoshi Tomita	05/09/2000
住所	Residence		
	Kawasaki, Japan		
国籍	Citizenship		
	Japan		
私書箱	Post Office Address		
	c/o FUJITSU LIMITED, 1-1, Kamikodanaka 4-chome,		
	Nakahara-ku, Kawasaki, 211-8588 Japan		
第八共同発明者名		Full name of eighth joint inventor, if any	
第八共同発明者の署名	日付	Eighth inventor's signature	Date
住所	Residence		
国籍	Citizenship		
私書箱	Post Office Address		
第九共同発明者名		Full name of ninth joint inventor, if any	
第九共同発明者の署名	日付	Ninth inventor's signature	Date
住所	Residence		
国籍	Citizenship		
私書箱	Post Office Address		
第十共同発明者名		Full name of tenth joint inventor, if any	
第十共同発明者の署名	日付	Tenth inventor's signature	Date
住所	Residence		
国籍	Citizenship		
私書箱	Post Office Address		